การพัฒนาซิลิกอนไนไตรด์เซรามิกที่มีต้นทุนการผลิตต่ำ

นายนิรุติ หวังหมู่กลาง

สถาบนวิทยบริการ

วิทยานิพนธ์นี้เป็นส่วนหนึ่งของการศึกษาตามหลักสูตรปริญญาวิทยาศาสตรมหาบัณฑิต สาขาวิชาเทคโนโลยีเซรามิก ภาควิชาวัสดุศาสตร์ คณะวิทยาศาสตร์ จุฬาลงกรณ์มหาวิทยาลัย ปีการศึกษา 2546 ISBN 974-17-4721-7 ลิขสิทธิ์ของจุฬาลงกรณ์มหาวิทยาลัย

DEVELOPMENT OF LOW COST ${\rm Si_3N_4}$ CERAMICS

Mr. Nirut Wangmooklang

สถาบนวทยบรการ

A Thesis Submitted in Partial Fulfillment of the Requirements for the Degree of Master of Science in Ceramic Technology Department of Materials Science Faculty of Science Chulalongkorn University Academic Year 2003 ISBN 974-17-4721-7

Thesis Title	Development of low cost ${\rm Si_3N_4}$ ceramics
Ву	Mr. Nirut Wangmooklang
Field of study	Materials Science
Thesis Advisor	Chair Professor Shigetaka Wada, Ph.D.
Thesis Co-advisor	Kuljira Sujirote, Ph.D.

Accepted by the Faculty of Science, Chulalongkorn University in Partial Fulfillment of the Requirements for the Master's Degree

..... Dean of Faculty of Science

(Professor Piamsak Menasveta, Ph.D.)

THESIS COMMITTEE

..... Chairman

(Associate Professor Saowaroj Chuayjuljit)

...... Thesis Advisor

(Chair Professor Shigetaka Wada, Ph.D.)

...... Thesis Co-advisor (Kuljira Sujirote, Ph.D.)

(Associate Professor Supatra Jinawath, Ph.D.)

...... Member

(Sirithan Jiemsirilers, Ph.D.)

นิรุติ หวังหมู่กลาง : การพัฒนาซิลิกอนไนไตรด์เซรามิกที่มีต้นทุนการผลิตต่ำ. (DEVELOPMENT OF LOW COST Si₃N₄ CERAMICS) อ. ที่ปรึกษา : ศ. ดร. ชิเกตากะ วาดะ, อ.ที่ปรึกษาร่วม : ดร. กุลจิรา สุจิโรจน์, จำนวนหน้า 106 หน้า. ISBN 974-17-4721-7

้งานวิจัยนี้เป็นการศึกษาการพัฒนาซิลิกอนในไตรด์ที่มีต้นทุนการผลิตต่ำ โดยใช้สารตั้งต้นและ ้วิธีการซินเทอร์ที่มีต้นทุนต่ำ คือใช้ผงเบต้าซิลิกอนในไตรด์ แมกนีเซีย และอะลูมินา เป็นสารตั้งต้น และทำ การซินเทอร์ในเตาเผาบรรยากาศปกติ การขึ้นรูปทำโดยการบดผสมวัสดุผง 90wt%Si₃N₄ + 5wt%MgO + 5wt%Al₂O₃ เป็นเวลา 4 ถึง 16 ชั่วโมง จากนั้นนำผงผสมอัดในแม่พิมพ์ เครื่องอัดทุกทิศทาง นำชิ้นตัว อย่างซิลิกอนในไตรด์มาซินเทอร์ในเบ้าอะลูมินาและกลบทับด้วยผงซิลิกอนในไตรด์และอะลูมินาในเตา เผาบรรยากาศปกติ ที่อุณหภูมิ 1500 °C ถึง 1700 °C เป็นเวลา 2 ชั่วโมง และมีการซินเทอร์ผงซิลิกอนไน ใตรด์ที่บดผสมกับสารปรับปรุงสมบัติเป็นเวลา 4 ถึง 8 ชั่วโมง ในเตาเผาบรรยากาศก๊าซไนโตรเจนที่ อุณหภูมิ 1750 °C ถึง 1800 °C ที่ความดันก๊าซไนโตรเจน 1 บรรยากาศ เป็นเวลา 2 ชั่วโมงเพื่อเปรียบ เทียบสมบัติของชิ้นงานหลังการซินเทอร์กับการซินเทอร์ในเตาเผาบรรยากาศปกติชิ้นงานซิลิกอนไนไตรด์ หลังการซินเทอร์ในเตาเผาบรรยากาศปกติทุกตัวอย่างมีค่าความหนาแน่นทางทฤษภูีมากกว่า 96 เปอร์เซ็นต์ที่อุณหภูมิ 1700 °C และชิ้นงานที่ได้จากการซินเทอร์ผงตัวอย่างที่ใช้เวลาในการบดผสมเป็น เวลา 4 ถึง 8 ชั่วโมง มีความแข็ง <mark>คว</mark>ามต้านทานต่อการแตกหัก และความต้านทานแรงดัดอยู่ในช่วง 12.7 ถึง 13.0 GPa 5.5 ถึง 6.1 MPa.m^{1/2} และ 238 ถึง 263 MPa ตามลำดับ ซึ่งมีค่าน้อยกว่าชิ้นงานที่ได้ จากการซินเทอร์ของผสมชนิดเดียวกันในเตาเผาบรรยากาศก๊าซไนโตรเจนที่มีความแข็ง ความต้านทาน ต่อการแตกหัก และความต้านทานแรงดัดอยู่ในช่วง 13.3 ถึง 13.8 GPa 6.1 ถึง 6.8 MPa.m^{1/2} และ 327 ถึง 406 MPa ตามลำดับ อย่างไรก็ตามความต้านทานแรงดัดยังมีค่าต่ำเมื่อเทียบกับทางการค้าซึ่งมีค่า 500 ถึง 600 MPa.

สถาบนวิทยบริการ จุฬาลงกรณ์มหาวิทยาลัย

ภาควิชาวัสดุศาสตร์ สาขาเทคโนโลยีเซรามิก ปีการศึกษา 2546

ลายมือชื่อนิสิต
ลายมือชื่ออาจารย์ที่ปรึกษา
ลายมือชื่ออาจารย์ที่ปรึกษาร่วม

##4472527823 : MAJOR CERAMIC TECHNOLOGY

Keyword : β-si₃N₄ / Air Atmosphere Furnace / Sintering / Magnesia /Alumina NIRUT WANGMOOKLANG : DEVELOPMENT OF LOW COST Si₃N₄ CERAMICS. THESIS ADVISOR : CHAIR PROF. SHIGETAKA WADA, Ph.D., THESIS CO-ADVISOR : KULJIRA SUJIROTE, Ph.D., 106 pp. ISBN 974-17-4721-7

Development of low cost Si_3N_4 ceramics is studied by using low cost starting materials, β -Si₃N₄ powder with MgO and Al₂O₃ additives, and sintering in air atmosphere furnace. Fabrication processes were performed by mixing and grinding $90wt\%Si_3N_4$ + 5wt%MgO + 5wt%Al₂O₃ powders for 4 to 16 hours. Then, the mixture was uniaxially and isostatically pressed into specimens. The specimens were placed in a set of specially designed alumina crucibles with silicon nitride and alumina packing powders and sintered in air atmosphere furnace at temperature ranging from 1500 to 1700°C for 2 hours. Sintering of β -Si₃N₄ powder in N₂ gas furnace at a temperature of 1750 to 1800 °C for 2 hours with N₂ gas pressure of 0.1 MPa was also operated in order to compare with the specimens sintered in air furnace. The theoretical densities of all specimens sintered in air furnace were over 96 % at the sintering temperature of 1700 °C. Vickers hardness, fracture toughness, and flexural strength of specimens sintered from mixed powder for 4 to 8 hours were from 12.7 to 13.0 GPa, 5.5 to 6.1 MPa.m^{1/2}, and 238 to 263 MPa, respectively. These values were less than the specimens sintered from the same powder in N₂ gas furnace of which the Vickers hardness, fracture toughness, and flexural strength are 13.3 to 13.8 GPa, 6.1 to 6.8 MPa.m^{1/2}, and 327 to 406 MPa, respectively. However, the values of flexural strength are relatively low, when compared with 500-600 MPa of commercial Si_3N_4 ceramics.

จุฬาลงกรณ์มหาวิทยาลย

Department Materials Science	Student's signature
Field of study <u>Ceramic Technology</u>	Advisor's signature
Academic year <u>2003</u>	Co-advisor's signature

Acknowledgements

This work was accomplished under the supervision of my thesis advisor, Professor Dr. Shigetaka Wada, Chair Professor of the Department of Materials Science, Faculty of Science, Chulalongkorn University. I would like to gratefully thank for his guidance, and invaluable suggestion throughout this research. My sincere appreciation is expressed to my thesis co-advisor, Dr. Kuljira Sujirote, National Metal and Materials Technology Center (MTEC), for her kindness understanding and valuable advice. I also would like to thank Associate Professor Dr. Supatra Jinawath for her suggestion and grammar proofreading of my thesis.

I also wish to express my appreciation to Mr. Thanakorn Wasanapienpong for his help and suggestions. Special thanks to the staff of Department of Geology, Faculty of Science, Chulalongkorn University for the kind support of phase analysis in this experiment. My thank is also extended to the staff of Scientific and Technological Research Equipment Center, Chulalongkorn University (STREC) for the help in hardness and fracture toughness investigation.

Many thanks are due to my friends and faculty members in the Department of Materials Science for friendship and support. Finally, I would like to express my deep appreciation to my family for their love, patience and understanding and I also would like to gratefully acknowledge MTEC for granting me the TGIST scholarship during my M.S. study.

ั้ สถาบนวทยบรการ จุฬาลงกรณ์มหาวิทยาลัย

CONTENTS

P	age		
Abstract (Thai)	iv		
Abstract (English)	v		
Acknowledgements	vi		
Chapter I Introduction	1		
1.1 Introduction	1		
1.2 Objectives	2		
Chapter II Literature review	3		
2.1 Crystal structure, properties and applications of Si_3N_4 ceramics	3		
2.1.1 Crystal structure of Si ₃ N ₄ ,	3		
2.1.2 Properties of Si ₃ N ₄	6		
2.1.3 Applications of Si ₃ N ₄ ceramics	7		
2.2 Silicon nitride powders	8		
2.3 Sintering mechanism of Si ₃ N ₄ ceramics	9		
2.4 Instability of Si ₃ N ₄ and Si ₃ N ₄ ceramics	10		
2.4.1 Oxidation of Si_3N_4	10		
2.4.2 Decomposition of Si ₃ N ₄	10		
2.5 Sintering of Si ₃ N ₄ ceramic in air furnace	.12		
2.6 Literature survey of sintering of β -Si ₃ N ₄ powder	.13		
Chapter III Experimental procedure	15		
3.1 Instrument and equipment	15		
3.2 Starting materials and chemicals	16		
3.3 Process flow chart and experimental conditions			
3.4 Sample preparations	.20		
3.4.1 Particle size reduction of Si_3N_4 powder	20		
3.4.1.1 Grinding Si_3N_4 powder by ball mill	20		
3.4.1.2 Grinding Si_3N_4 powder by attrition mill	21		
3.4.2 Grinding and mixing of Si_3N_4 powder with additives	21		
3.4.3 Sintering of Si_3N_4	22		

CONTENTS (Cont.)

		Page
	3.4.3.1 Sintering in air atmosphere furnace	22
	3.4.3.2 Sintering in N ₂ gas furnace	23
3.5	Property measurements and characterizations	23
	3.5.1 Particle size distribution of starting materials and mixed powde	ers 23
	3.5.2 Oxygen analysis and theoretical density calculation of mixed	
	powder	
	3.5.3 Mass change measurement	
	3.5.4 Bulk density and relative density	
	3.5.5 Identification of material and determination of phase content in	$\mathrm{Si}_3\mathrm{N}_4$ by
	X-ray diffraction analysis	
	3.5.6 Observation of microstructure by scanning electron microscop	e
	(SEM)	29
	3.5.7 Vickers hardness and fracture toughness	31
	3.5.8 Flexural strength test by biaxial bending test at room temperatu	ure33
Chapter	IV Results and discussion	
4.1	Particle size distribution of Si_3N_4 and mixed powder	
	4.1.1 Characteristics of Si ₃ N ₄ (SN-F2) powder	36
	4.1.2 Particle size distribution of Si ₃ N ₄ powder	37
4.2	Oxygen content of mixed Si_3N_4 powders	
4.3	Mass loss	41
4.4	Bulk density and relative density	
4.5	Deterioration of Al ₂ O ₃ crucible	
4.6.	Phase compositions of Si_3N_4 raw powder and specimens	47
	4.6.1 Si ₃ N ₄ raw powder	
	4.6.2 Sintered specimens	
4.7	Microstructures	52
4.8.	Mechanical properties	56
	4.8.1 Vickers hardness and fracture toughness	54
	4.8.2 Flexural strength	59

CONTENTS (Cont.)

3-
Chapter V Conclusion
Chapter VI Future work
References
Appendices
Appendix A
Appendix B
Appendix C73
Appendix D77
Appendix E
Appendix F93
Appendix G
Appendix H105
BIOGRAPHY 106

สถาบันวิทยบริการ จุฬาลงกรณ์มหาวิทยาลัย

LIST OF TABLES

Page

Х

Table 2.1 Properties of silicon nitride ceramics	3
Table 2.2 Expected fields of application of silicon nitride ceramics	7
Table 2.3 Literature survey of sintering of eta -Si $_{3}$ N $_{4}$ powder with various additives,	
sintering temperature and gas pressure13	3

Table 3.1 List of instrument and equipment used in this experiment
Table 3.2 List of raw materials and chemicals used in this experiment
<u>Table 3.3</u> Grinding and mixing conditions of Si_3N_4 mixtures by attrition mill
Table 3.4 Sintering conditions of this experiment
<u>Table 3.5</u> Grinding conditions of Si_3N_4 powder by ball mill
<u>Table 3.6</u> Grinding conditions of Si_3N_4 powder by attrition mill
<u>Table 3.7</u> Grinding/mixing conditions of Si_3N_4 mixture by attrition mill
Table 3.8 Calculated theoretical density of mixed powder for 6 h
Table 3.9 Calculated theoretical density of mixed powder from various grinding
condition
<u>Table 3.10</u> Sintered Si_3N_4 specimens selected for XRD analysis
<u>Table 3.11</u> Sintered Si_3N_4 specimens selected for SEM analysis
Table 3.12 Specimens for Vickers hardness (Hv), fracture toughness (K $_{\rm IC}$) and flexural
strength test
<u>Table 4.1</u> Phase content of specimens sintered in air atmosphere furnace and in N_2 gas
furnace
<u>Table 4.2</u> Hv and K_{IC} of specimens sintered in air furnace at 1700 ^o C for 2 h
<u>Table 4.3</u> Hv and K_{1C} of specimens sintered in N_2 gas furnace at 1700 $^{\circ}C$ and 1800 $^{\circ}C$
for 2 h

Table 4.4	Biaxial flexura	l strength o	of specimens	sintered in	air atmospher	e furnace	. 59
<u>Table 4.5</u>	Biaxial flexural	strength c	of specimens	sintered in	N ₂ gas furnace		. 59

LIST OF FIGURES

Page
<u>Fig 2.1</u> (a) The basis of crystalline Si_3N_4 tetrahedra (b) Outline of silicon nitride crystal
structure
Fig 2.2 (a) AB layer, which is repeated in the stacking sequence of $\beta\text{-}\text{Si}_{_3}\text{N}_{_4}$ (b) Positions
of Si atoms above the base of the unit cell in $eta ext{-Si}_3N_4$ (c) AB and CD layers,
which are alternated in the stacking sequence of $eta ext{-Si}_3N_4$ (d) Positions of Si
atoms above the base of the unit cell in β - Si $_3N_4$ 5
<u>Fig 2.3</u> Sintered Si_3N_4 components
Fig 2.4 Schematic diagram illustrating the morphological development of
β -Si ₃ N ₄ grains during consolidation9
<u>Fig 2.5</u> Stability diagram for Si ₃ N ₄ , where Si vapor is in equilibrium
with Si_3N_4 as a function of N_2 pressure and temperature11
Fig 3.1 Flow chart of specimen preparation and characterization
Fig 3.2 Schematic of the crucible structure
<u>Fig 3.3</u> Schematic of specimens setting for sintering in N_2 gas furnace
Fig 3.4 Sample preparation flow chart for SEM analysis
Fig 3.5 Biaxial-Flexure Strength Fixture
Fig 3.6 Relationship between X and B value for 3-point bending strength test
<u>Fig 4.1</u> SEM image of Si_3N_4 powder, SN-F2 grade
Fig 4.2 Particle size distributions of milled Si_3N_4 powder (SN-F2) by ball mill
at various milling time37
<u>Fig 4.3</u> Particle size distributions of milled Si_3N_4 powder by attrition mill at
various milling times
<u>Fig 4.4</u> SEM image of milled Si_3N_4 powder by attrition mill for 10 h (E10H)
<u>Fig 4.5</u> Particle size distributions of mixed Si_3N_4 powder by attrition mill at
various milling times
<u>Fig 4.6</u> Oxygen contents of mixed Si_3N_4 powder as a function of mixing time
Fig 4.7 Mass loss of specimens sintered in air atmosphere and N_2 atmosphere

LIST OF FIGURES (Cont.)

Page
furnaces as a function of temperature41
Fig 4.8 Bulk density of sintered specimens with various kinds of milling
conditions as a function of sintering temperature43
Fig 4.9 Relative density of sintered specimens with various kinds of milling
conditions as a function of sintering temperature43
Fig 4.10 Phase diagram of MgO-Al ₂ O ₃ -SiO ₂ system
<u>Fig 4.11</u> Aspect of inside wall of Al_2O_3 crucible after sintering
<u>Fig 4.12</u> X-ray diffraction pattern of Si_3N_4 raw powder (SN-F2)47
Fig 4.13 XRD patterns of specimens sintered in air atmosphere furnace at1500 °C49
Fig 4.14 XRD patterns of specimens sintered in air atmosphere furnace at 1700 °C50
<u>Fig 4.15</u> XRD patterns of specimens sintered in N_2 gas furnace, E6H51
Fig 4.16 SEM micrographs of plasma etched E8H specimens sintered in air
furnace at various temperature for 2 h ; (a) 1500 °C, (b) 1650 °C53
Fig 4.17 SEM micrographs of plasma etched H16H specimens sintered in air
furnace at various temperature for 2 h ; (a) 1500 °C, (b) 1650 °C54
<u>Fig 4.18</u> SEM micrographs of plasma etched E8H specimens sintered in N_2
furnace for 2 h ; (a) 1750 °C and (b) 1800 °C55
<u>Fig 4.19</u> Top view of indent of E8H specimen sintered in air furnace at 1700 $^{\circ}$ C for 2 h
<u>Fig 4.20</u> SEM micrographs of specimens sintered in air furnace at 1700 $^{\circ}$ C for 2 h ;
(a) $m{lpha}$ -Si $_3N_4$ powder and (b) $m{eta}$ -Si $_3N_4$ powder

CHAPTER I

1.1 Introduction

Silicon nitride ceramics have been intensively studied for many years because of their great potential for structural applications at room and elevated temperatures. This due to their excellent mechanical properties in combination with good corrosion and thermal shock resistance.¹⁻³⁾ Silicon nitride is a covalent ceramic and is difficult to consolidate by solid state sintering because of a low diffusivity.^{1,4)} Hence, sintering additives such as MgO, Y₂O₃, CeO₂, Y₂O₃-Al₂O₃ must be used to enhance densification.⁴⁻

An α -Si₃N₄ powder with Y₂O₃-Al₂O₃ additives is one of the most popular system for densification of Si₃N₄ because the resulted ceramics show excellent mechanical properties ⁸⁻⁹⁾. However, α -Si₃N₄ powder and Y₂O₃ are so expensive and must be sintered in a furnace with applied N₂ gas pressure.⁶⁻⁹⁾ As a result, the production cost of silicon nitride ceramics rises so high.

Sintering of β -Si₃N₄ powder has been investigated by several researchers. However, they used high gas pressure sintering at high temperature with Y₂O₃-Al₂O₃, Y₂O₃-Nd₂O₃ sintering additives ¹⁰⁻¹⁷⁾ and the experimental results of them such as mechanical properties were satisfied. The results are still uneconomical because of the high costs incurred by the sintering methods and expensive sintering additives. Therefore, in this research we focus on the sintering of β -Si₃N₄ powder (SN-F2) with MgO-Al₂O₃ additives, because β -Si₃N₄ powder (SN-F2) and MgO are less expensive than α -Si₃N₄ and Y₂O₃ powders, respectively. And sintering in air atmosphere furnace, invented by Prof. Dr. Shigetaka Wada et al., was promising.¹⁸⁾ According to this system, we expect to get low production cost of Si₃N₄ ceramics. The scope of this experiment is to study the sintering of β -Si₃N₄ powder with MgO-Al₂O₃ additives, which is sintered in a temperature range between 1500 °C to 1700 °C at an interval of 50 °C, in air atmosphere furnace. Also sintering in N₂ gas furnace at a temperature range between 1750 °C and 1800 °C was performed as the reference to the result of sintering in air.



1.2 The objectives of this research

- 1. To get the optimal condition for grinding and mixing of Si₃N₄ powder with sintering additives.
- 2. To study the sinterability of β -Si₃N₄ powder with MgO-Al₂O₃ additives and mechanical properties of sintered β -Si₃N₄ ceramic.
- 3. To pursue the technological knowledge on the sintering of low cost Si_3N_4 powder and sintering additives.

สถาบันวิทยบริการ จุฬาลงกรณ์มหาวิทยาลัย

CHAPTER II

LITERATURE REVIEW

2.1 Crystal structure, properties and applications of Si_3N_4 ceramics

2.1.1 Crystal structure of Si₃N₄

The tetrahedra structure (SiN_4) is the basis of crystalline Si_3N_4 (Fig. 2.1a) ¹⁹. The silicon atoms are in the center site of irregular nitrogen tetrahedral and each nitrogen atom belongs to three tetrahedra as shown in Fig 2.1a and 2.1b. ²⁰ It is indicated that the SiN₄ tetrahedra introduces an open structure with large voids.



<u>Fig 2.1</u> (a) The basis of crystalline Si_3N_4 tetrahedra¹⁹⁾. (b) Outline of silicon nitride crystal structure²⁰⁾

Silicon nitride occurs in two polytypes, the α and β phases^{19,21)}. Both are hexagonal, but differ in the sequence in which Si-N layers are arranged in the c-axis direction. The β -Si₃N₄ has an ABAB stacking sequence of layers with a unit cell of formula Si₆N₈, while α -Si₃N₄ has an ABCD stacking sequence of layers and twice the unit cell formula, Si₁₂N₁₆. Since in α -Si₃N₄ the stacking repeats after twice the number of layers, it has approximately twice the c-axis lattice parameter of the β phase (see Table 2.1).²²⁾

Fig 2.2a shows the atomic arrangement in a single AB layer sequence. The N atoms indicated by the filled triangles and the layer of Si atoms shown as filled circles lie in a plane forming the base of the unit cell. The Si atoms in this layer are indicated by "0" in the schematic in Fig. 2.2b. The next layers of N and Si atoms are shown as open circles and triangles, and are located at the "1/2" position in Fig. 2.2b. Noticed that a ring-like configuration of Si-N-Si-N bonds exists, with either 8 or 12 membered rings (similar configuration exists in the crystalline silicates). In β -Si₃N₄ the next AB layer is superimposed directly over the first, so that a continuous interstitial channel parallel to the c-axis forms around the site surrounded by 12 Si-N bonds. In α -Si₃N₄ the CD layer shown in Fig. 2.2c is superimposed on the AB layer. This isolates the large interstices formed by the 12-membered ring. The height of Si atoms above the base of the unit cell in the α phase is shown in Fig.2.2d. The availability of large interstitial sites in both structures facilitates the formation of oxynitride solid solutions.

สถาบันวิทยบริการ จุฬาลงกรณ์มหาวิทยาลัย



Fig. 2.2 (a) AB layer, which is repeated in the stacking sequence of β -Si₃N₄. (b) Positions of Si atoms above the base of the unit cell in β -Si₃N₄. (c) AB and CD layers, which are alternated in the stacking sequence of α -Si₃N₄. (d) Positions of Si atoms above the base of the unit cell in α -Si₃N₄.

2.1.2 Properties of Si₃N₄

The properties of $\mathrm{Si_3N_4}$ ceramics are shown in Table 2.1.

Decomposition temperature ($^{\circ}$ C)	1900
Theoretical density ($a cm^{-3}$)	
	2 160 2 100
	3.100-3.100
p-pnase	3.19-3.202
Density (g cm [°]):	
dense Si ₃ N ₄	90-100 % th.d.*
Coefficient of thermal expansion	
(20-1500 °C) (10 ⁻⁶ °C ⁻¹)	2.9-3.6
Thermal conductivity (RT) (W m ⁻¹ K ⁻¹):	
dense Si ₃ N ₄	15-50
Thermal diffusivity (RT) (cm ² sec ⁻¹):	
dense Si ₃ N ₄	0.08-0.29
Specific heat (J kg ⁻¹ °C ⁻¹)	700
Electrical resistivity (RT) (Ω cm)	~ 10 ¹³
Microhardness (Vickers, MN m ⁻²)	1600-2200
Young's modulus, (RT) (GN m ⁻²):	
dense Si ₃ N ₄	300-330
Flexural strength (RT) (MN m ⁻²):	
dense Si ₃ N ₄	400-95
Fracture toughness (MN m ^{-3/2}):	
dense Si ₃ N ₄	3.4-8.2
Thermal stress resistance	
Parameter $R = \sigma_{F}(1-v)/\alpha E$ (°C)	
and $R' = R\lambda(10^3 - V) W m^{-1}$:	
dense Si_3N_4	<i>R</i> = 300-780 <i>R</i> ′ = 7-32

Table 2.1 Properties of silicon nitride ceramics 22)

* Theoretical density is dependent on the type and composition of consolidation aids (t.d. of pure $Si_3N_4 = 3.2 \text{ g cm}^{-3}$)

2.1.3 Applications of Si₃N₄ ceramics

Silicon nitride has better high temperature properties, such as strength, creep and oxidation resistance, than metals. In addition, its low thermal expansion coefficient gives good thermal shock resistance compared with most other ceramic materials.

Table 2.2 and Fig. 2.3 show typical Si_3N_4 components, for several application fields. Heat or wear resistant components, such as mechanical seals, cutting tools and glow plugs, are shown.^{20,23)}

Application fields	Components	
Wear-and corrosion-resistant	Bearings, mechanical seals, blast	
components	honing nozzles, vane pump parts,	
	chemical pump parts	
Metal treatment components	Aluminum diecast parts (metal melt	
	guides, plungers, cylinders, and	
	piston cylinders); wire-drawing roller	
	pulleys and dies; steel forming parts	
Tools	Cutting tolls	
Heat-resistant jigs:		
Heat-protecting parts	Thermal-insulation ceramic tiles,	
	heat-shielding plates, plasma	
	insulators	
High-temperature test jigs	Strength test jigs (bend and tensile)	

Table 2.2 Expected fields of application of silicon nitride ceramics ²³⁾





<u>Fig. 2.3</u> Sintered Si_3N_4 components ^{20,24)}

2.2 Silicon nitride powders

There are four main technologies to produce Si_3N_4 powder.²⁵⁻²⁸⁾ Si_3N_4 powders synthesized by the method a) and d) are commercially produced.

a) Nitridation of silicon powder :

3Si + 2N₂ Si₃N₄ -----(1)
b) Gas-phase deposition :
$$\rightarrow$$

3SiCl₄ + 4NH₃ \rightarrow Si₃N₄ + 12HCl \uparrow -----(2)

c) Carbo-thremal reduction of SiO₂ in notrogen atmosphere :

$$3SiO_2 + 6C + 2N_2$$
 $Si_3N_4 + 6CO$ -----(3)

d) Precipitation of silicon diimide and thermal decomposition :

$$SiCl_4 + 6NH_3$$
 $Si(NH)_2 + 4NH_4Cl$ -----(4)
 $3Si(NH)_2$ $Si_3N_4 + 2NH_3$ -----(5)

There are marked differences in the type and amount of impurities, in the size and morphology of the powder particles and the phase composition of powders obtained from these techniques. By varying the processing conditions, however, the properties of powders produced by any of these techniques may be changed, particularly the phase composition, degree of crystallinity and particle morphology.

The prices of Si_3N_4 powders depend on the characteristic of powders such as / ratio, purity and mean particle size or specific surface area.

2.3 Sintering mechanism of Si₃N₄ ceramics

Pure Si_3N_4 is difficult to densify because of the high covalent nature of the Si-N bonds.²⁹⁾ The self-diffusion coefficient is very low in comparison to other ceramic materials. Usually the densification of Si_3N_4 is achieved through the acceleration of mass transport by the formation of a liquid phase during sintering. The liquid phase used for sintering is an oxynitride liquid formed by the reaction of sintering additives with the SiO₂ existing on the surface of the Si_3N_4 powder particles. The most commonly used additives are Al_2O_3 in combination with Y_2O_3 , La_2O_3 , lanthanoids or MgO.^{6,9,30)}

The polymorphic forms of the starting powders (α or α) have a definite influence on the morphology of the consolidated structure. When the starting powder contains mainly α phase material, the particles first dissolute into grain boundary liquid and precipitate as long rod like acicular grains of α . When the starting powder is phase, the phase particles merely coalesce and grow.

The dissolution-precipitation mechanisms of both α and phase powders during liquid phase sintering are shown in Fig 2.4.



 $\underline{\text{Fig 2.4}}$ Schematic diagram illustrating the morphological development of $\beta\text{-Si}_3\text{N}_4$ grains during consolidation $^{\scriptscriptstyle 31)}$

2.4 Instability of Si₃N₄ and Si₃N₄ ceramics

 Si_3N_4 is thermodynamically unstable with respect to oxidation. Moreover, Si_3N_4 decomposes at high temperature and Si_3N_4 ceramics show mass loss reaction during sintering.

2.4.1 Oxidation of Si₃N₄

The oxidation occurs by two mechanisms, passive oxidation and active oxidation as shown in reaction (1) and (2), respectively.³²⁾

$$Si_3N_4(s) + 3O_2(g) \rightarrow 3SiO_2(l) + 2N_2(g)$$
 -----(6)

$$2Si_{3}N_{4}(s) + 3O_{2}(g) \rightarrow 6SiO(g) + 4N_{2}(g)$$
 -----(7)

Silicon nitride and silicon nitride ceramics are easily oxidized in air at elevated temperature above 1000 °C. The oxidation mechanisms are passive oxidation in the atmosphere of $PO_2 \ge 10^2$ and active oxidation at less than 10^2 Pa. ³²⁾ A SiO₂ protective layer is formed on a surface of specimen by passive oxidation and active oxidation occurs with formation of volatile SiO.

2.4.2 Decomposition of Si₃N₄

Fig 2.5 shows the stability diagram of Si_3N_4 , silicon nitride does not have a melting point but decomposes under 0.1 MPa N_2 at 1900 °C. From the thermodynamic viewpoint, Si_3N_4 (s) decomposes to Si (l) and N_2 (g) at the sintering temperature in vacuum according to the reaction (8).³³⁾

$$Si_3N_4$$
 (s) \rightarrow 3Si (l) + 2N₂ (g) -----(8)



<u>Fig 2.5</u> Stability diagram for Si_3N_4 , where Si vapor is in equilibrium with Si_3N_4 as a function of N_2 pressure and temperature

สถาบันวิทยบริการ

From the stability diagram, N_2 gas pressure as high as $P_{N2} > 10^6$ Pa is essential to obtain dense Si_3N_4 ceramics at high sintering temperature. In other words, high N_2 gas pressure in the furnace effectively suppresses the mass loss during sintering.

2.5 Sintering of Si₃N₄ ceramic in air furnace

Non-pressurized sintering of Si₃N₄ ceramic in N₂ gas furnace is thought to be a low cost fabrication. But N₂ gas furnace is still special comparing to air furnace. According to Wada et al. in 2001, Si₃N₄ ceramic could be sintered without serious oxidation in air atmosphere furnace.¹⁸⁾ To isolate Si_3N_4 specimen from air, it is set in two Al_2O_3 crucibles that are filled with Si_3N_4 powder in the inner crucible and Al_2O_3 powder in the outer crucible. When Si₃N₄ ceramics are sintered in the mentioned sagger, there are two different sources of oxygen: one is the oxygen in the sagger, the other is the oxygen diffusing into the sagger through a gap. The amount of oxygen calculated from the volume of the sagger is not so large. When the sagger is filled with Si₂N₄ powder, the powder consumes oxygen in the sagger via Reaction (6) and then, when PO_2 in the sagger decreases to below 10^2 Pa, Reaction (7) occurs, three moles of O₂ (g) change to 6 mol of SiO (g) and 4 mol of N₂ (g). Therefore, once active oxidation occurs, the generated gas increases in volume and flows out through the gap of the sagger, thereby decreasing the oxygen partial pressure in the sagger and disturbing the diffusion of air from outside of the sagger. After most of the oxygen in the sagger has reacted with Si_3N_4 , the generated gas flow stops and air will again diffuse into the sagger. However, since the sagger is filled with Si₃N₄ powder, oxygen diffusing into the sagger reacts with Si_3N_4 powder near the gap of the sagger and these will not reach the Si_3N_4 specimen. Therefore, Si₃N₄ ceramics could be sintered without serious oxidation and mass loss in air atmosphere furnace.

สถาบนวิทยบริการ จุฬาลงกรณ์มหาวิทยาลัย

2.6 Literature survey of sintering of β -Si₃N₄ powder

Sintering of β -Si₃N₄ powder with Y₂O₃-Al₂O₃ or Y₂O₃-Nd₂O₃ sintering additives by using N₂ gas atmosphere furnace was investigated by several researchers. The experimental conditions and mechanical properties are shown in Table 2.3.

<u>Table 2.3</u> Literature survey of sintering of β -Si₃N₄ powder with various additives, sintering temperature and gas pressure

Authors	Sintering additives	β phase content in powder (%)	Sintering conditions	Flexural strength (MPa) / Fracture toughness (MPa m ^{1/2})	References
Mitomo et al.	Y ₂ O ₃ -Al ₂ O ₃	>99	1950 [°] C, N ₂ 10 MPa	467 / 5.8	17
Hirosaki et al.	Y ₂ O ₃ - Nd ₂ O ₃	95	1900-2000 [°] C, N ₂ 10-30 MPa	515-689 / 8.5-10.3	34
Hirosaki et al.	Y ₂ O ₃ -Al ₂ O ₃	95	1800-1900 [°] C, N ₂ 1-10 MPa	358-900 / 3.1-7.1	12
Hirosaki et al.	Y ₂ O ₃ - Nd ₂ O ₃	>99	1900 [°] C, N ₂ 10 MPa	600-843 / 5.3-7.1	13
Ogasawa et al.	Y ₂ O ₃ - Nd ₂ O ₃	>99	1900-2000 [°] C, N ₂ 10-30 MPa	678-746 / 7.2-9.0	15
Okamoto et al.	Y ₂ O ₃ -Al ₂ O ₃	>99	1900 [°] C, N ₂ 1 MPa	689 / 6.4	16

In 1990, Mamoru Mitomo et al., ¹⁷⁾ investigated in the topic of "Grain growth during gas-pressure sintering of β -silicon nitride". This work was performed using over 99 mass % of β -Si₃N₄ powder and Y₂O₃-Al₂O₃ as sintering additives. The sample was sintered at 1950 °C under N₂ gas pressure of 10 MPa.

In 1993, Naoto Hirosaki et al.,³⁴⁾ investigated the effect of grain growth of β -silicon nitride on strength, Weibull modulus, and fracture toughness using 95 mass % of β -Si₃N₄ powder with Y₂O₃ and Nd₂O₃ additives. The sintering process was performed using the temperature range of 1900 °C to 2000 °C at N₂ gas pressure of 10-30 MPa. Then, after one and two years, they studied in the titles, "Sintering of Y₂O₃-Al₂O₃-doped β -Si₃N₄ powder and mechanical properties of sintered materials"¹²⁾, and "Effect of purification of β -Si₃N₄ powder on the strength of sintered materials"¹³⁾, respectively. Both of research work were performed using β -Si₃N₄ powder with Y₂O₃, Al₂O₃ and Nd₂O₃ additives, and sintering at the temperature range of 1800 °C to 1900 °C under the N₂ gas pressure of 1-10 MPa.

In 1995, Toshio Ogasawara et al,¹⁵⁾ and Yusuke Okamoto et al ¹⁶⁾ investigated in the topics of "Fatigue behavior of silicon nitride ceramics prepared from β -phase powder" and "Mechanical properties and oxidation resistance of silicon nitride produced from low purity β -powder", respectively. In the work of Ogasawara and Okamoto works, high β -phase content of Si₃N₄ powder and Y₂O₃, Al₂O₃ and Nd₂O₃ additives were used. The sintering processes were operated at the temperature range of 1900 °C to 2000 °C under N₂ gas pressure of 10-30 MPa for Ogasawara work. In the case of Okamoto, the sintering temperature of 1900 °C at 1 MPa of N₂ gas pressure was used.

All of the mechanical properties obtained by these researchers are shown in Table 2.3. Most of the experimental results show satisfactory mechanical properties. However, expensive sintering additives and the high cost sintering processes are used.

CHAPTER III

EXPERIMENTAL PROCEDURE

3.1 Instrument and equipment

Instruments and equipments used for this experiment are shown in Table 3.1. <u>Table 3.1</u> List of instrument and equipment used in this experiment

Instrument and equipment	Trademarks	Types/Models
Attrition mill	Szegvari Attritor	-
Roller (for ball mill)	U.S. Stoneware	CZ-02003
Electrical balance	Sartorius	BP 221S
Particle size analyzer	Shimadzu	SA-CP2
Drying oven	Bulglin	DICF
Oxygen/Nitrogen determinator	LECO	TC-436 DR
Pressing machine	-	NT-100H
Cold isostatic press	Cobe Steel	Dr. CIP
Vernier caliper	Mitutoyo	-
Alumina crucible	Nikkato	SSA-S
Electrical furnace	Lindberg	LCC256PCOMC (1700 °C)
High temperature furnace (N ₂ atmosphere)	Fujidempa	FVP HP-R-5, FRET-20
X-ray diffractometer	Bruker	D8-Advance
Grinding/Polishing machine	Buehler	Phoenix 4000
Optical microscope	Olympus	BX60M
Scanning electron microscope	JEOL	JSM-5410L
Hardness tester	Zwick GmbH	Zwick 3212
Biaxial bending tester	Intro enterprise	LLOYD 500

3.2 Starting materials and chemicals

Silicon nitride powder, sintering additives, packing powder and grinding medium as listed in Table 3.2 were used. The properties of SN-F2, MJ-30, AKP-30 and A-11 are shown in Table A-1, A-2, A-3 and A-4 in appendices.

Raw materials / Chemicals	Trademarks / Manufactures	Grades	Chemical compositions (%)
Silicon nitride powder	Denki Kagaku Kogyo	SN-F2	eta phase = 100
Magnesium oxide	Iwatani Chemicals	MJ-30	MgO = 99.9
Aluminium oxide	Taimei Chemicals	AKP-30	Al ₂ O ₃ = 99.99
	Fuji Kasei	A-11	Al ₂ O ₃ = 99.7
Ethanol (C ₂ H ₅ OH)	Carlo Erba	AR	Purity = 99.8
n-hexane (C ₆ H ₁₄)	Fisher Chemicals	AR	Purity = 99.9
Sodium hexametaphosphate	Fluka chemicals	AR	-

Table 3.2 List of raw materials and chemicals used in this experiment



3.3 Process flow chart and experimental conditions

The process flow chart is shown in Fig. 3.1. Raw Si_3N_4 powder (SN-F2) and sintering additives were ground and mixed by attrition mill using ZrO_2 pot (1100 cm³) and Si_3N_4 balls (diameter 5 mm) for 4, 6, 8, 10 and 16 h. Ethanol and n-hexane were used as solvent. In case of using n-hexane as the solvent, grinding time was only 10 and 16 h, and it was evaporated at room temperature before drying at 100 °C. When the solvent was ethanol, the slurry was dried at a temperature around 80 °C. The dried powder was sieved through 100 mesh. The sieved powders were formed into tablets of 20 mm in diameter and 5 mm in thickness.

Initially, the mixed powders without binder were compacted by a uniaxial press at 20 MPa. Then the specimens were cold isostatic pressed (CIP) to obtain higher density of green compacts with a pressure of 200 MPa. The specimens were set in an Al_2O_3 crucible with Si_3N_4 (SN-F2) and Al_2O_3 (A-11) packing powders. Sintering was performed in an air atmosphere furnace at a temperature range between 1500 °C to 1700 °C at the interval of 50 °C. Some specimens were sintered in N_2 gas furnace at a temperature range between 1500 °C to 1700 °C at the interval of 50 °C and 1800 °C under a N_2 gas pressure of 0.1 MPa by with a heating and cooling rates of 10 °C/min, and a soaking time of 2 h. Bulk density, and mass change were determined for all specimens. Phase composition, microstructure, Vickers hardness, fracture toughness and flexural strength of selected specimens were measured and observed. All grinding and sintering conditions are shown in Table 3.3 and Table 3.4, respectively.

Bulk density, water absorption and apparent porosity were measured by Archimedes' method.³⁵⁾ Crystalline phase compositions were identified by X-ray diffractometer (XRD). The morphology of polished surface was observed by scanning electron microscope (SEM). Vickers hardness and fracture toughness were measured by indentation method.³⁶⁻³⁷⁾ Then, the flexural strength was determined by a biaxial-bending test in conformity with ASTM-F394-78.³⁸⁾





characterization

Powder codes	Grinding/mixing	Grinding/mixing	Grinding/mixing
	mediums	times (h)	speed (rpm)
E4H	ethanol	4	550
E6H	ethanol	6	550
E8H	ethanol	8	550
E10H	ethanol	10	550
E16H	ethanol	16	550
H10H	n-hexane	10	550
H16H	n-hexane	16	550

<u>Table 3.3</u> Grinding and mixing conditions of Si_3N_4 mixtures by attrition mill

Table 3.4 Sintering conditions of this experiment

Powder	Temperature(°C)		Heating/Cooling rate	Soaking
codes	Air fur <mark>nace</mark>	N ₂ gas furnace ¹⁾	([°] C/min)	time (hr)
E4H	1500-1700	1750-1800	10/10 (10/10) ²⁾	2 (2) ³⁾
E6H	1500-1700	1750-1800	10/10 (10/10) ²⁾	2 (2) ³⁾
E8H	1500-1700	1750-1800	10/10 (10/10) ²⁾	2 (2) ³⁾
E10H	1500-1700	-	10/10	2
E16H	1500-1700	-	10/10	2
H10H	1500-1700		10/10	2
H16H	1500-1700	L'IN-EU	10/10	2

¹⁾ = N_2 gas pressure is 0.1 MPa with flow rate of 2 lit/min.

 $^{2)}$ = Heating and cooling rate of sintering in N₂ gas furnace.

 $^{3)}$ = Soaking time of sintering in N₂ gas furnace.

3.4 Sample preparations

3.4.1 Particle size reduction of Si₃N₄ powder

The commercial Si₃N₄ powder (SN-F2) was used as the raw Si₃N₄ powder. The powder was composed of 100 % β -phase content and small amount of impurities (Fe and Na). The oxygen content is around 1.18 wt %. However, the mean particle size of SN-F2 quite large and difficult to get high density of sintered bodies.³⁹⁾

In order to reduce the size of Si_3N_4 particles, two methods for grinding and mixing Si_3N_4 powder were used, ball mill and attrition mill were used in this experiment.

<u>3.4.1.1 Grinding Si₃N₄ powder by ball mill</u>

The commercial Si_3N_4 powder were ground by ball milling in a Si_3N_4 pot, using Si_3N_4 balls with 150 cm³ of ethanol and 40 g of powder for 192 h, and the rotation speed was 150 rpm. At every 24 h the slurry was sampled and dried in the oven at 80 °C, for particle size analysis. Then, the particle size distributions of powder were measured by particle size analyzer. Grinding conditions of Si_3N_4 powder are shown in Table 3.5.

Pot and balls	${ m Si_3N_4}$ pot (500 cm³), ${ m Si_3N_4}$ balls ($igoplus$ 5 mm) 250 cm³ (Half a volume
F OL ANU DAIIS	of pot)
Medium	150 cm ³ of ethanol ⁴⁰⁾
Powder	$Si_{3}N_{4}$ powder (40 g of the mixed powder) ⁴⁰⁾
Rotation speed	150 rpm ⁴⁰⁾
Time	192 h

<u>Table 3.5</u> Grinding conditions of Si_3N_4 powder by ball mill

3.4.1.2 Grinding Si₃N₄ powder by attrition mill

Table 3.6 shows the grinding conditions and the ratio of Si_3N_4 powder, Si_3N_4 balls and grinding medium (ethanol). At 1, 3, 5, 7 and 10 h, the slurry was sampled and dried in the oven at 80 °C, for particle size analysis.

<u>Table 3.6</u> Grinding conditions of Si_3N_4 powder by attrition mill

Pot and balls	ZrO_2 pot (1100 cm ³), Si ₃ N ₄ balls (ϕ 5 mm)	
Medium	ethanol	
Ratio of raw powder : solvent : balls	100 g : 300 g : 1200 g (1:3:12) ⁴⁰⁾	
Rotation speed	550 rpm	
Time	10 h	

3.4.2 Grinding and mixing of Si₃N₄ powder with additives

Table 3.7 shows the grinding/mixing conditions Si_3N_4 mixture of with composition 90 wt% Si_3N_4 powder, 5 wt% MgO and 5 wt% Al_2O_3 .

<u>Table 3.7</u> Grinding/mixing conditions of Si_3N_4 mixture by attrition mill

Pot and balls	ZrO_2 pot (1100 cm ³), Si ₃ N ₄ balls (ϕ 5 mm)	
Medium	ethanol and n-hexane	
Ratio of raw powder :	100 g* : 300 g** : 1200 g (1:3:12) ⁴⁰⁾	
solvent : balls	100 g* : 225 g*** : 1200 g (1:2.25:12)	
Rotation speed	550 rpm	
Times	(4, 6, 8, 10, and 16 h)**, (10 and 16 h)***	

* = Si_3N_4 powder 90 g + MgO 5 g + Al_2O_3 5 g

3.4.3.1 Sintering in air atmosphere furnace

 AI_2O_3 is a candidate material for crucible as described in previous paper.¹⁸⁾ Crucible structure is shown in Fig.3.2 the specimens were set in the small AI_2O_3 crucible (50 cm³) with Si_3N_4 packing powder of which particle size was larger than 75 µm. Then, the small crucible was set in a larger crucible (280 cm³), which was filled with AI_2O_3 packing powder (A-11).



3.4.3.2 Sintering in N₂ gas furnace

The specimens were embedded in the powder mixture of Si_3N_4 and BN, in a BN sagger as shown in Fig. 3.3. Sintering was performed using N_2 gas furnace (HIGH MULTI-5000) at a temperature range between 1750 °C and 1800 °C for 2 h under a N_2 gas pressure of 0.1 MPa and a flow rate of 2 lit/min.



Fig. 3.3 Schematic of specimens setting for sintering in N₂ gas furnace

3.5 Property measurements and characterizations

3.5.1 Particle size distribution of starting materials and mixed powders

Sedimentation method (Shimadzu SA-CP2) was used for investigation of particle size distribution of raw Si_3N_4 powder (SN-F2) and ground or mixed powders.

Approximately 0.5 g of the powder was dispersed in 50 cm³ water, which was 0.2 wt% aqueous solution of sodium hexametaphosphate. Sample particles were completely dispersed by magnetic stirrer, at least for 20 min.

Then, sample slurry was de-agglomerated in an ultrasonic bath. Gravity or centrifugal mode was selected for powder with diameter larger than 10 μ m or smaller than 8 μ m, respectively. Sedimentation depth No.3 and rotation speed of 500 or 1000 rpm were used as the condition for analysis depending on the fineness of powders.

3.5.2 Oxygen analysis and theoretical density calculation of mixed powder

Oxygen contents in raw powder and mixed powder were measured by using Nitrogen/Oxygen determinator (LECO TC-436 DR) at the Siam Research and Development Co.,Ltd.

In this experiment, the contents of oxygen before and after milling of mixed powder are analyzed. The analyzed amount of oxygen in the mixed powder includes oxygen from MgO and Al_2O_3 . Therefore, the oxygen belongs to MgO and Al_2O_3 is subtracted from the analyzed amount. Then oxygen belongs to SiO₂ is determined.

One example of theoretical density calculation of mixed powder is as follows:

90 × 0.0118

1.06

For the composition, 90 wt% Si_3N_4 , 5 wt% MgO and 5 wt% Al_2O_3 at a milling time for 6 h, oxygen content of raw Si_3N_4 (SN-F2) and mixed powder are 1.18 wt% and 7.24 wt% , respectively.

a) Calculation of wt% oxygen in raw powder.

Oxygen (wt %) = Si_3N_4 wt% × (1.18/100)

b) Calculation of % SiO₂ in raw powder

 SiO_2 (wt%) = [(60.08/2×16)] × 1.06

=

1.99
c) Calculation of wt % of oxygen in MgO and Al_2O_3 .

Wt % of oxygen in oxide $\rm M_aO_b$ can be calculated as follows:

Wt % O
$$(M_a O_b) = \left(100 \times \frac{b \times MW_o}{MW_{M_a O_b}}\right) \times [wt\% \text{ oxide}]$$
 ------(1)
Wt % Oxygen of (5 wt% Al₂O₃) = (3×16/101.96) × 5

= 2.35 Where :

a	=	Mole of metal
b	=	Mole of oxygen
MW _o	=	Molecular weight of oxygen
MW _{MaOb}	=	Molecular weight of oxide

From equation (1) :

Wt % Oxygen of (5 wt% MgO) = (16/40.31) × 5 = 1.98

d) Calculation of the incremental oxygen content in mixed powder.

The analyzed oxygen content of mixed powder is 7.24 wt%

```
Therefore : Oxygen (increased) = 7.24 - 1.98 - 1.18 - 2.35
= 1.73 \text{ wt\%}
From 1.73 wt% of oxygen, wt% of SiO<sub>2</sub> in Si<sub>3</sub>N<sub>4</sub> is :
```

 SiO_2 (wt%) = [(60.08)/(2×16)] × 1.73

= 3.25

Total SiO₂ in mixed Si₃N₄ powder is
$$1.99 + 3.25 = 5.24$$
 wt%

e) Theoretical density of glassy phase is calculated from SiO_2 , MgO and Al_2O_3 compositions, because the glassy phase containing in Si_3N_4 is made from them, using theoretical density value of 2.2 g/cm³, 3.64 g/cm³ and 4.0 g/cm³ for SiO_2 , MgO and Al_2O_3 , respectively.

The density of glass could be estimated as follows:

Glass density = \sum (Weight fraction of oxide × density of oxide) = [(5.24/15.24)×2.2] + [(5/15.24)×3.64] + [(5/15.24)×4] = 0.76 + 1.19 + 1.31 = 3.26 g/cm³

f) The theoretical density of mixed powder is the sum of the theoretical density of Si_3N_4 and glassy phase. The theoretical density of mixed powder is calculated as 3.22 g/cm³.

Table 3.8 Calculated theoretical density of mixed powder for 6 h

Powder	Real	Theoretical	Density
composition	composition	density (g/cm ³)	(g/cm ³)
Si ₃ N ₄	84.76	3.21	2.72
Glass	15.24	3.26	0.50
Total	100	-	3.22

All results calculated for mixed powders at various grinding time are shown in Table 3.9.

		Analyzed					Calculated
Grinding	Grinding	oxygen	Rea	al compos	theoretical		
medium	time (h)	content	Si ₃ N ₄ *	SiO ₂ *	MgO	Al_2O_3	density
		(wt%)	9				(g/cm ³)
-	0	1.18	88.01	1.99	5	5	3.26
	4	6.92	85.36	4.64	5	5	3.22
	6	7.24	84.76	5.24	5	5	3.22
ethanol	8	7.88	83.56	6.44	5	5	3.20
	10	8.97	81.51	8.49	5	5	3.19
	16	9.54	80.44	9.56	5	5	3.17
n-	10	10.00	79.58	10.42	5	5	3.16
hexane	16	11.30	77.14	12.86	5	5	3.15

Table 3.9 Calculated theoretical density of mixed powder from various grinding conditions

* = the value from calculation

3.5.3 Mass change measurement

The mass loss of each specimen was calculated from the weight measurement of specimens before (W_B) and after sintering (W_A). The mass loss is calculated as follows:

Mass change (%) =
$$((W_B - W_A)/W_B) \times 100$$

3.5.4 Bulk density and relative density

Bulk density was measured by Archimedes' method.³⁵⁾ The detail was omitted. Relative density was calculated from bulk density and theoretical density which is shown in Table 3.9.

<u>3.5.5</u> Identification of material and determination of phase content in Si_3N_4 by X-ray diffraction analysis

The qualitative analyses of raw Si_3N_4 (SN-F2) and sintered specimens were determined by X-ray diffraction (D8-Advance, Bruker Co., Ltd.). The value of 2θ around 10-70°, and the scanning speed of 2°/min were used as conditions. The specimens analyzed by X-ray diffraction analysis are shown in Table 3.10.

Sample preparation

The sintered specimen was ground in an Al_2O_3 mortar. Then, the powder was screen through sieve number 230 (70 μ m). Then, about 1-2 grams of powder was used for X-ray diffraction analysis.

Samples	Sintering in	air furnace	Sintering in N	2 gas furnace
ล	1500 °C	1700 °C	1750 °C	1800 °C
E4H	0	0	2	0.1
E6H	0	0	0	0
E8H	0	0		
E10H	0	0		
E16H	0	0		
H10H	0	0		
H16H	0	0		

Table 3.10 Sintered Si₃N₄ specimens selected for XRD analysis

3.5.6 Observation of microstructure by scanning electron microscope (SEM)

The microstructures of polished surface were characterized by SEM. Sintered Si_3N_4 specimens selected for SEM analysis are shown in Table 3.11. The procedure of sample preparation for polished surface analysis is shown in Fig 3.4.

Sintering in air furnace					Sintering	in N_2 gas	
Samples		Sinter	ing in all lu	ITTACE		furn	ace
	1500 °C	1550 °C	1600 °C	1650 °C	1700 °C	1750 °C	1800 °C
E4H						0	0
E6H			a and			0	0
E8H	0	0	0	0	0	0	0
H16H	0	0	0	0	0		

<u>Table 3.11</u> Sintered Si_3N_4 specimens selected for SEM analysis





Fig 3.4 Sample preparation flow chart for SEM analysis

*Plasma etching and SEM analysis were performed by Mr.Thanakorn Wasanapienpong at Tokyo Institute of Technology (TIT), Japan.

3.5.7 Vickers hardness and fracture toughness

Sample preparation:

The Vickers hardness and fracture toughness of the sintered specimens were measured by Vickers indentation method and calculated according to JIS-R1610³⁶⁾ and JIS-R1607, ³⁷⁾ respectively. For this experiment, sintered specimens that are selected for Vickers hardness and fracture toughness testing are shown in Table 3.12.

Test specimen was ground with 200 grit diamond wheel and then polished with 400, 800 and 1,200 grit SiC papers (Buehler grinding paper) down to 15.30 μ m, and followed by 6, 3 and 1 μ m diamond paste. The surface was examined at intervals using optical microscope. After polishing, specimens were washed with alcohol in an ultrasonic bath to remove dirt and debris from the surfaces. Vickers indentation was applied at a load of 98.07 N(10 kgf) in conformity with JIS standard (Designation R 1610-1991) using microhardness tester.(Zwick 3212, Zwick GmbH & Co.)

Calculation:

Vickers hardness, (Hv) is calculated by the following equation:

$$Hv = 1.8544 \left(\frac{P}{(d)^2}\right)$$
Where: $P = Load (N)$

$$d = Diagonal length (mm)$$

Fracture toughness, $(K_{\rm IC})$ is calculate by the following equation in conformity with JIS R1607-1995

$$K_{1C} = 0.018 \left(\frac{E}{Hv}\right)^{1/2} \left(\frac{P}{C^{3/2}}\right)$$
Where: $C = Crack \text{ length (mm)}$
 $E = Young' \text{ modulus} \sim 300 \text{ GPa}$
 $Hv = Vickers \text{ hardness}$

<u>Table 3.12</u> Specimens for Vickers hardness (Hv), fracture toughness (K_{1C}) and flexural strength test

	Sintering in air	Sintering in N ₂ gas		
Samples	furnace	furnace		
	1700 °C	1750 °C	1800 °C	
E4H	0	0	0	
E6H	0	0	0	
E8H	0	0	0	

สถาบนวทยบรการ จุฬาลงกรณ์มหาวิทยาลัย

3.5.8 Flexural strength test by biaxial bending test at room temperature

Flexural strength was measured by a biaxial-bending test in conformity with ASTM F : 394-78. $^{38)}$ The figure of testing equipment is shown in Fig. 3.5.

Sample preparation:

The selected specimens for flexural strength tests are shown in Table 3.12. The specimens were ground to flat surface by # 170 diamond wheel. Next, their tensile surfaces were ground with 200 and 400 grit diamond wheel followed by polishing with 800 and 1200 grit SiC papers (Buehler grinding paper), respectively. Then, the finished surfaces were polished using 6, 3 and 1 μ m diamond paste, respectively. All tests were performed using LLOYD 500, Intro enterprise Co., Ltd. The crosshead speed was constant at 0.5 mm/min.





Calculation:

Flexural strength is calculated by the following equations.

S =
$$\frac{-0.2387 P \times (X - Y)}{d^2}$$
 -----(1)

$$X = \left\{ \left(1 - \nu\right) \times \ln\left(\frac{B}{C}\right)^2 \right\} + \left\{ \frac{\left(1 - \nu\right)}{2} \times \left(\frac{B}{C}\right)^2 \right\}$$
 -----(2)

$$Y = \left\{ \left(1 - \nu\right) \times \left(1 + \ln\left(\frac{A}{C}\right)^2\right) \right\} + \left\{ \left(1 - \nu\right) \times \left(\frac{A}{C}\right)^2 \right\}$$
 -----(3)

Where:

S = Maximum center tensile stress (MPa)

P = Total load causing fracture (N)

- μ = Poisson's ratio, 0.23
- A = Radius of support circle (12.5 mm)
- B = Radius of loaded area or ram tip (2.5 mm)

C = Radius of specimen (mm)

d = Specimen thickness at fracture origin (mm)

ุลถาบนวทยบรการ จุฬาลงกรณ์มหาวิทยาลัย

The relation between X and B, when C = 13.5, is shown in Fig 3.6.



Relationship between X and B value

Fig 3.6 Relationship between X and B value for 3-point bending strength test

Miss. Bongkoch ⁴¹⁾ used the Si₃N₄ ball of 2.5 mm. radius as the ram tip for her master thesis. The contact radius of the ball was 0.125 mm. From Fig 3.6, it was understood that X value changed much when contact radius B changed just a little at the range of B < 0.5 mm. The ram tip radius of 2.5 mm was thought to be not so sensitive to the deviation of B. Considering this fact, the ram tip radius of 2.5 mm was selected.



CHAPTER IV

RESULTS AND DISCUSSION

4.1 Particle size distribution of Si_3N_4 and mixed powder

4.1.1 Characteristics of Si₂N₄ (SN-F2) powder

Figure 4.1 shows the SEM image of Si_3N_4 powder, SN-F2 grade. Its particle size distribution is shown in Figure 4.2 and 4.3. As shown in Figure 4.1, this starting powder consists of wide distribution, large agglomerated particles, large acicular shaped particle and small particles. The particle size distributions measured by sieve analysis are shown in Appendix B. The mean particle size about 22 μ m was measured from the particle size distribution curve (Figure 4.2 or 4.3, as-received powder). Therefore, in order to get high density of sintered materials this powder must be crushed.^{22,39}



Fig 4.1 SEM image of Si₃N₄ powder, SN-F2 grade

4.1.2 Particle size distribution of Si₃N₄ powder

Two kinds of grinding method, which are ball mill and attrition mill, were used to investigate the reduction of Si_3N_4 powder. The particle size distribution curves of milled SN-F2 powder by ball mill and attrition mill are shown in Figure 4.2 and 4.3, respectively.



<u>Fig 4.2</u> Particle size distributions of milled Si_3N_4 powder (SN-F2) by ball mill at various milling times

The mean particle size of milled Si_3N_4 powder by ball mill for 192 h and attrition mill for 10 h are 0.78 µm and 0.73 µm, respectively. The particle morphology of milled powder is shown in Figure 4.4. The particle shapes after ground are equiaxed small grains size, hence acicular grains were crushed. Both ball mill and attrition mill grinding methods could reduced the particle size down to sub-micrometer size. However, in the case of attrition mill was more time economical than ball mill. Therefore, the attrition mill method was more suitable for grinding and mixing of Si_3N_4 powder with sintering additives than ball mill.





<u>Fig 4.3</u> Particle size distributions of milled Si_3N_4 powder by attrition mill at various milling times



<u>Fig 4.4</u> SEM image of milled Si_3N_4 powder by attrition mill for 10 h (E10H)



<u>Fig 4.5</u> Particle size distributions of mixed Si_3N_4 powder by attrition mill at various milling times

4.2 Oxygen content of mixed Si₃N₄ powders

Two kinds of solvents, ethanol and n-hexane, were used as grinding and mixing medium. The oxygen content of mixed Si_3N_4 powder was measured by Oxygen/Nitrogen determinator. The results of analysis are shown in Table 3.9. The Increment of total oxygen content caused by increasing the mixing times is shown in Figure 4.6.



Fig 4.6 Oxygen contents of mixed Si₃N₄ powder as a function of mixing time

The oxygen content is increased with increasing mixing time in both ethanol and n-hexane as mixing mediums. In case of ethanol as a solvent, Prof. Dr. Shigetaka Wada reported that,⁴⁰⁾ the most of increment of oxygen content came from two main reactions, which are the reaction of Si_3N_4 with moisture in the air and the mechanochemical reaction between Si_3N_4 and ethanol. The reaction of H_2O and Si_3N_4 was considered to be as follows:

$$6H_2O(I) + Si_3N_4(s) \rightarrow 3SiO_2(s) + 4NH_3(g)$$
 -----(1)

The mechanochemical reaction was complicated reaction, Hirano et al. quoted.⁴²⁻⁴³⁾ that the Si-O-R bond was formed on the surface of the Si_3N_4 powder according to the reaction in equation (2).

Si-OH + R-OH
$$\rightarrow$$
 Si-O-R + H₂O -----(2)

Considering that this reaction may take place in the attrition mill, it can naturally be conceived that the H_2O generated acts according to equation (1).

In the case of n-hexane as a solvent (H10H, H16H), in this experiment the author did not exactly examine the process of the reaction between Si_3N_4 and n-hexane. The oxygen content of milled powder is higher than that ethanol at the same mixing time. The reason for this may be supposed that n-hexane more active than ethanol. The reaction of n-hexane with the moisture in air may happen easier than the reaction in an ethanol, because this experiment was performed in an open system.

4.3 Mass loss

The relationship between mass loss and sintering temperature of both specimens sintered in air and N_2 atmosphere furnace are shown in Figure 4.7. The original data are shown in Appendix Table D-1 and Table D-3, respectively.



<u>Fig 4.7</u> Mass loss of specimens sintered in air atmosphere and N_2 atmosphere furnaces as a function of temperature

In case of sintering in N_2 gas furnace, the major mass loss reaction was presumed to be reaction (3). ⁵⁰⁾ Since the SiO (g) partial pressure increases by increasing temperature, as shown in Fig C-1 in Appendix C, the mass loss values increased as a function of temperature.

$$Si_3N_4(s) + 3SiO_2(l) \rightarrow 6SiO_2(g) + 2N_2(g)$$
 -----(3)

In the case of sintering in air furnace, mass loss of specimens was not increased so much even when increased the sintering temperature, but increased as a function of oxygen content in Si_3N_4 powder. The major mass loss will be resulted from the same reaction as sintering in N₂ gas furnace (reaction (3)). However, there are big atmosphere difference in the partial pressure of O₂ (g) and N₂ (g) in these two sintering methods. It might be caused the difference of mass loss phenomenon.

Moreover, the mass loss might occur according to the decomposition of MgO additive to Mg (g) and O_2 (g), because MgO is not stable at high temperature. The MgO (g) and Mg (g) partial pressures are shown in Appendix Fig C-1.



4.4 Bulk density and relative density

Figure 4.8 and 4.9 show bulk density and relative density of the specimens sintered in air atmosphere compared with specimens sintered in N_2 gas furnace, respectively. The original data are shown in Appendix Table D-2 and D-4.



Fig 4.8 Bulk density of sintered specimens with various kinds of milling conditions as a function of sintering temperature



<u>Fig 4.9</u> Relative density of sintered specimens with various kinds of milling conditions as a function of sintering temperature

Figure 4.8 shows changes of bulk density with sintering temperature. For the specimens sintered in air atmosphere furnace, E4H, E6H, E8H, E10H, and E16H could achieve almost full density at the temperature over 1650 °C. However, at the lowest temperature (1500 °C), we found that the relative densities of sintered specimens except E4H were over 92 % of theoretical density (see Fig 4.9). The high densities at the low sintering temperature were caused by the formation of liquid phase. Because, MgO and Al_2O_3 additives, and surface silica of Si_3N_4 powder could form as liquid phase at low temperature.⁴⁶⁾

In the case of MgO addition, the eutectic temperature of the mixture MgO-SiO₂ is about 1540 °C ⁴⁶⁾ and this can be lowered by addition of AI_2O_3 , as shown in Figure 4.10. With increasing temperature, the viscosity of the liquid is decreased. As a result, rearrangement and subsequently the solution-diffusion-precipitation processes are enhanced. ²²⁾ Thus, the specimens could be sintered at low temperature. However, in the case of E4H, the specimens did not achieve high density because of its larger mean particle size than other ones and smaller amount of glassy phase.

The densities of specimens sintered in air furnace of over 96 % of theoretical density. The high density was achieved at the sintering temperature of 1650 °C and 1700 °C, which was the same as specimens sintered in N_2 atmosphere, because the compositions of specimens consist of much amount of additives and oxidized SiO₂ in this experiment. Therefore, the specimens could be sintered at low sintering temperature. However, densities of specimens sintered in air furnace were less than the specimens sintered in N_2 gas furnace, because of sintering temperature of N_2 gas furnace was higher than that of the air furnace. In the other word, the higher densities were attributed to the higher sintering temperature.



<u>Fig 4.10</u> Phase diagram of MgO-Al₂O₃-SiO₂ system

4.5 Deterioration of Al_2O_3 crucible

After sintering for several times, the whole color of the inside wall of Al_2O_3 crucible changed from white to gray and became swollen. It was alter confirmed that some powder reacted with the wall of Al_2O_3 crucible and formed layer of porous product. Its phase contents were measured by Piyaporn.⁴⁷⁾ Phase analysis by X-ray diffraction revealed three types of materials, Si_3N_4 , corundum, and aluminum silicon oxide nitride ($Si_{12}Al_{18}O_{39}N_8$). Figure 4.11 shows the outlook observation of Al_2O_3 crucible after sintering for several times.



Fig 4.11 Aspect of inside wall of Al₂O₃ crucible after sintering

Piyaporn reported that, the phase content on reacted surface of AI_2O_3 crucible is aluminum silicon oxide nitride ($Si_{12}AI_{18}O_{39}N_8$). Aluminum silicon oxide nitride was supposed to come from either of the following reactions.

$$6SiO_{2}(I) + 2Si_{3}N_{4}(s) + 9AI_{2}O_{3}(s) = Si_{12}AI_{18}O_{39}N_{8}(s) -----(1)$$

$$12SiO (g) + 9AI_2O_3 (s) + 4N_2 (g) = Si_{12}AI_{18}O_{39}N_8 (s) -----(2)$$

On the surface of AI_2O_3 crucible, there was not so much SiO_2 (I) so it must be difficult thinking that it was the reaction between solid (Si_3N_4) and solid (AI_2O_3) . On the contrary, SiO and N₂ are both gases. Then, reaction (2) might be more possible. AI_2O_3 crucible cracked after using for several times. The difference of thermal expansion between $Si_{12}AI_{18}O_{39}N_8$ (s) and AI_2O_3 may cause those cracks.

4.6 Phase compositions of Si₃N₄ raw powder and specimens

4.6.1 Si₃N₄ raw powder

Phase compositions of Si₃N₄ raw powder were confirmed by X-ray diffractometer (XRD). The XRD pattern is shown in Figure 4.12, Si₃N₄ raw powder consists of β -Si₃N₄ and small amount of silicon oxynitride. That is, the powder is almost 100% β phase.



<u>Fig 4.12</u> X-ray diffraction pattern of Si_3N_4 raw powder (SN-F2)

4.6.2 Sintered specimens

Phase compositions of sintered specimens were measured by XRD. Phase contents of sintered specimens are show in Table 4.1. Figure 4.13 and 4.14 show the XRD patterns of the specimens sintered in air atmosphere furnace at the temperature of 1500 °C and 1700 °C, respectively. The original data are shown in Appendix E.

<u>Table 4.1</u> Phase content of specimens sintered in air atmosphere furnace and in N_2 gas furnace

Samples	Sintering in air furnace		Sintering in N	I_2 gas furnace
	1500 °C	1700 °C	1750 °C	1800 °C
E4H	β	β		
E6H	β + z	β + z	β	β
E8H	β + 0 + z	β + z	6	
E10H	β + 0 + z	β + z		
E16H	β + 0 + z	β + 0 + z	0	
нтон	β + 0	β+0	การ	
H16H	β + 0	β + 0	์ทยาล	2

Note : $\beta = \beta - Si_3N_4$

 $O = Sinoite (Si_2N_2O)$

 $Z = Baddeleyite, ZrO_2$







Fig 4.14 XRD patterns of specimens sintered in air atmosphere furnace at 1700 °C

Silicon oxynitride can be formed by reaction between Si_3N_4 and surface SiO_2 .⁴⁸⁻⁴⁹⁾ The reaction is shown in equation (4).

$$Si_3N_4(s) + SiO_2(s) \rightarrow 2Si_2N_2O(s)$$
 ------(4)

From the X-ray diffraction patterns of sintered specimens, it is shown that Si_2N_2O phase is present in the specimens that contain much amount of SiO_2 (long milling time). At the sintering temperature of 1500 °C, Si_2N_2O phase is found as a trace in E8H and could be obviously observed in the specimens with higher SiO_2 content (E10H, E16H, H10H, and E16H). In the specimen of 1700 °C, Si_2N_2O phase can not be seen in E8H and E10H. However, in the specimens E16H, H10H, and H16H Si_2N_2O still appeared, because their SiO_2 content are high.⁴⁸⁾ However, the content of Si_2N_2O was not analyzed quantitative in this work. In case of sintering in N_2 gas furnace, only β -Si₃N₄ phase is presented as shown in Figure 4.15.

In addition, baddeleyite phase (ZrO_2) was seen in some specimens. It was a contaminant from the wearing of ZrO_2 pot of the attrition mill.



<u>Fig 4.15</u> XRD patterns of specimens sintered in N_2 gas furnace, E6H

4.7 Microstructures

Microstructures of sintered specimens were observed by scanning electron microscope (SEM). Figure 4.16 shows polished surface of E8H specimens sintered in air furnace at 1500 °C and 1650 °C. The micrograph reveals the development of grain growth. With increasing temperature, the solution-diffusion-precipitation process starts and superimpose on the rearrangement process. The driving force for this second stage is the higher solubility at the contact points of the particle caused by capillary forces as well as the differences in the chemical potentials between small and large particles, which leads to an enhanced solution of small particles.²²⁾ Therefore, when increasing the sintering temperature, the grain growth of the β grains occurs.

Figure 4.17 shows polished surface of H16H (highest amount glass phase) specimens sintered in air furnace at 1500 °C and 1650 °C. It is analyzed by XRD that these specimens are composed of β -Si₃N₄ and Si₂N₂O. From these micrographs, it is concluded that small needle-like crystal in Figure 4.17 might be Si₂N₂O. Moreover, grain growth is developed as a function of temperature as well.

Microstructures of specimens sintered in N_2 gas furnace are shown in Figure 4.18. In the case of sintering in N_2 furnace, the microstructures are also mainly equiaxed grains and grain size is slightly increased by increasing sintering temperature.

In this work, β -Si₃N₄ powder were used. Thus, in this case no α -to- β conversion occur. Both of specimens sintered in air and N₂ gas furnace show mostly equiaxied small grain, because the sintering temperature and time are not high enough to accelerate the grain growth of β -Si₃N₄. V.K. Sarin reported that the large elongated grains of Si₃N₄ from β powder appear at the sintering temperature over 1800 °C and sintering time over 4 hrs. ³¹⁾ The SEM micrographs of other specimens are attached in Appendix F.



(a)



(b)

<u>Fig 4.16</u> SEM micrographs of plasma etched E8H specimens sintered in air furnace at various temperature for 2 h; (a) 1500 $^{\circ}$ C, (b) 1650 $^{\circ}$ C



(a)



(b)

<u>Fig 4.17</u> SEM micrographs of plasma etched H16H specimens sintered in air furnace at various temperature for 2 h; (a) 1500 $^{\circ}$ C, (b) 1650 $^{\circ}$ C





<u>Fig 4.18</u> SEM micrographs of plasma etched E8H specimens sintered in $\rm N_2$ furnace for 2 h; (a) 1750 °C and (b) 1800 °C

4.8 Mechanical properties

4.8.1 Vickers hardness and fracture toughness

Top view of indent is shown in Figure 4.19. The size of the indent and crack was measured, and the Vickers hardness (Hv) and fracture toughness (K_{IC}) were calculated by the equation in 3.5.7. The calculation results are shown in Appendix G.



<u>Fig 4.19</u> Top view of indent of E8H specimen sintered in air furnace at 1700 $^{\circ}$ C for 2 h

Samples	Hv	K _{IC}	Bulk density
800	(GPa)	(MPa m ^{1/2})	(g/cm ³)
E4H	12.7 ± 0.2	5.9 ± 0.4	3.09
E6H	13.0 ± 0.3	6.1 ± 0.3	3.13
E8H	12.7 ± 0.2	5.5 ± 0.1	3.14

<u>Table 4.2</u> Hv and K_{IC} of Si_3N_4 sintered in air furnace at 1700 $^{\circ}C$ for 2 h

The specimens of E4H, E6H, and E8H sintered at 1700 °C were selected for the measure of Vickers hardness (Hv) and fracture toughness (K_{IC}), because of their low oxygen contents. As shown in Table 4.2, both of Hv and K_{IC} values are not so different, in the compositions.

In Appendix H, properties of TOSHIBA's specimen are shown. Comparing its Hv, 16.8 GPa and K_{IC} , 5.4 MPa.m^{1/2} to the results of our specimens, Hv, 12.7-13.0 GPa and K_{IC} , 5.5-6.1 MPa.m^{1/2}, the K_{IC} values of our specimens are similar to that of TOSHIBA's specimen. However, hardness of our specimens are lower than the commercial one. The reason for this might be due to the much amount of glassy phase in our specimens.

Vickers hardness and fracture toughness of specimens sintered in N_2 gas furnace are shown in Table 4.3. The K_{IC} values are higher than the specimens sintered in air furnace. The reason for this might be come from the larger grain in the specimens sintered in air (see Fig 4.16 and 4.15 (e)). Peillon and Thevenot reported that the fracture toughness is proportional to the grain diameter square root ⁵¹⁾ and it increases with the fraction of the large grains.

<u>Table 4.3</u>	Hv and K_{1c} of specimens sintered in N_2 gas furnace at 1700 °C and 1800 °C
for 2 h	

Temperature	Samples	Hv	K _{IC}	Bulk density
(°C)		(GPa)	(MPa m ^{1/2})	(g/cm ³)
6161	E4H	13.3 ± 0.1	6.8 ± 0.7	3.15
1750	E6H	13.7 ± 0.2	6.5 ± 0.3	3.17
N 10	E8H	13.4 ± 0.1	6.1 ± 0.3	6 C 3.17
-	E4H	13.6 ± 0.3	6.6 ± 0.7	3.18
1800	E6H	13.8 ± 0.1	6.4 ± 0.7	3.17
	E8H	13.5 ± 0.6	6.8 ± 0.2	3.17

Moreover, the Vickers hardness values of specimens sintered in N_2 furnace are a little higher than the ones in an air furnace, because of the higher densities. However, Vickers hardness values are still lower than TOSHIBA's specimen.

Comparison of Vickers hardness and fracture toughness of specimens sintered in air furnace with different starting Si_3N_4 powder (α -powder and β -powder) are compared. In case of Piyaporn's thesis experiment ⁴⁷⁾, using α -Si₃N₄ powder as raw material, hardness and fracture toughness of sintered specimens are 16.0 GPa and 5.0 MPa m^{1/2}, respectively. The hardness of Piyaporn's specimens is higher than that of our specimens. It is come from the fact that α phase, which hardness is higher that that of β phase, remained in her specimen. On the contrary, fracture toughness of our specimens is higher than the specimens from α -powder, which is attributed to grain diameter of specimens produced from β -powder are larger than the α -powder as seen in Figure 4.20.



<u>Fig 4.20</u> SEM micrographs of specimens sintered in air furnace at 1700 °C for 2 h; (a) α -Si₃N₄ powder and (b) β -Si₃N₄ powder

4.8.2 Flexural strength

The averages biaxial flexural strength of specimens sintered both in air and N_2 gas furnace are shown in Table 4.4 and 4.5, respectively. The calculation results are attached as Table G-4, G-5, and G-6 in appendix G. In case of sintering in air furnace, the minimum strength value was 219 MPa and maximum was 263 MPa. The minimum and maximum values of specimens sintered in N_2 gas furnace were 261 MPa and 406 MPa, respectively.

Table 4.4 Biaxial flexural strength of specimens sintered in air atmosphere furnace

Sintering	Strength (MPa)				
temperature (^o C)	E4H	E6H	E8H	E10H	
1650				219 ± 36	
1700	238 ± 25	263 ± 45	252 ± 42		

<u>Table 4.5</u> Biaxial flexural strength of specimens sintered in N_2 gas furnace

Sintering		Strength (MPa)	
temperature (^o C)	E4H	E6H	E8H
1750	406 ± 14	327 ± 49	328 ± 79
1800	307 ± 46	261 ± 34	390 ± 63



The difference in flexural strength of specimens sintered in air furnace with different mixing time were not significant. The strength values were lower than that those the specimens sintered in N_2 gas furnace. The causes are thought as follows:

1) Much amount of glass phase

As seen in Table 3.6, the oxygen content in the mixed powder increased with the mixing times. That cause the increase in the quantity of SiO_2 in mixed powder. As a result, the total content of glassy phase increased. It is reported that increasing the glassy phase lowered the strength lower.⁵²⁾

2) Low aspect ratio of β -grains

Generally, the structures with elongated grains show better mechanical properties than that with equiaxed ones. Since the elongated grains cause linking each other, crack deflection and pull out of crystal increase. These cracks deflection and pull out crystals absorb energy and lead to an enlarged fracture surface. ⁵³⁾ In this experiment, the grain morphology of specimens sintered both in air and N₂ gas furnace show small equiaxed grains, almost no elongated grains. Therefore, the flexural strength of specimens become low.

สถาบันวิทยบริการ จุฬาลงกรณ์มหาวิทยาลัย
CHAPTER V

CONCLUSION

- 1. β -Si₃N₄ powder (SN-F2) could be ground down to 1 μ m by both ball mill and attrition mill. However, attrition mill was selected for mixing raw powder with sintering additives due to high efficiency.
- 2. β -Si₃N₄ (SN-F2) was successfully sintered in air furnace. The relative densities after sintering at 1700 ^oC for 2 h were over 96 % of theoretical density. It was very close to the density of Si₃N₄ sintered in N₂ gas furnace. Mass losses of sintered specimens do not depend on sintering temperature, but depend on the quantity of glassy phase. Mass loss is presumed to be the reaction of Si₃N₄ and SiO₂.

$$Si_3N_4(s) + 3 SiO_2(l) \rightarrow 6 SiO(g) + 2 N_2(g)$$

However, the tendency mass loss phenomenon of the specimens sintered in air furnace differed from that of sintered in N_2 gas furnace.

- 3. The materials of both specimens sintered in air and N₂ gas furnace consisted of mostly small equiaxed grains of β -Si₃N₄ and much amount of glassy phase, the average grain size of β -Si₃N₄ was less than 5 μ m.
- 4. Vickers hardness and fracture toughness of Si_3N_4 sintered in air furnace were in the range of 12.7 to 13.0 GPa and 5.5 to 6.1 MPa.m^{1/2}, respectively. These values were a little lower than the specimens sintered in N_2 gas furnace. Comparing with commercial Si_3N_4 (TOSHIBA's standard bar) the hardness values are lower but fracture toughness were a little higher.
- 5. The flexural strength values of specimens sintered in air and N_2 gas furnaces were in the range of 219 to 263 MPa and 261 to 406 MPa, respectively. These values were relatively low compared to ~ 600 MPa of commercial Si₃N₄.

CHAPTER VI

FUTURE WORK

- 1. In this experiment, the oxygen content of mixed powder was increased with mixing time. As a result, SiO_2 content increased too much by the long time milling. The much amount of SiO_2 degrades the mechanical properties. Therefore, it is important to develop a crushing technology without increasing SiO_2 .
- Al₂O₃ crucible reacted with Si₃N₄ and SiO and deteriorated or cracked after several times of usage. It causes high cost in production. Therefore, it is essential to find a technology or material, which delays the deterioration of crucible.
- 3. The mechanical strength of sintered specimens was not so high comparing with the commercial silicon nitride ceramics, because of the much amount of glassy phase. Therefore, we should improve the mechanical properties of these materials by reduction of the glassy phase in the future work.

References

- M. Herrmann, H. Klemm, and C. Schubert. Silicon nitride based hard materials. <u>Handbook of Ceramic Hard Materials</u>. Dresden: WILEY-VCH Verlag GmbH, 2000.
- Chihiro Kawai and Akira Yamakawa. Effect of Porosity and Microstructure on the Strength of Si₃N₄: Designed Microstructure for High Strength, High Thermal Shock Resistance, and Facile Machining. <u>J. Am. Ceram. Soc</u>. Vol.80, No.10 (1997) : 2705-2708.
- G. R. Terwilliger. Properties of Sintered Si₃N₄. <u>J. Am. Ceram. Soc</u>. Vol.57, No.1(1974)
 : 48-49.
- Randall M. German. <u>Liquid Phase Sintering</u>. New York and London : Plenum press, 1985.
- 5. S. Hampshire and K. H. Jack. The Kinetics of Densification and Phase Transformation of Nitrogen Ceramics. <u>Proc. Bri. Ceram. Soc</u>. 31, (1981) : 37-48.
- 6. Pavol Sajgalik and Miroslav Haviar. Pressureless Sintering of Si₃N₄ with Y₂O₃ and Al₂O₃ Additives-Compatibility of Powder Beds. <u>Ceramics International</u>. 18, (1992) : 279-283.
- H. Yang, G. Yang and R. Yuan. Pressureless Sintering of Silicon Nitride with Magnesia and Ceria. <u>Materials research Bulletin</u>. Vol.33, No.10 (1998) : 1467-1473.
- M. Yoshimura et al. Grain Size Controlled High-Strength Silicon Nitride Ceramics.
 <u>J. Ceram. Soc. Japan</u>. Vol.103, No.4 (1995) : 407-408.
- E. Tani et al. Gas-Pressure Sintering of Si₃N₄ with Concurrent Addition of Al₂O₃ and 5 wt% Rare Earth Oxide: High fracture Toughness Si₃N₄ with Fiber-Like Structure. <u>Am. Ceram. Soc. Bull</u>. Vol65, No.9 (1986) : 1311-1315.
- 10. N. Hirosaki et al. Gas-Pressure Sintering of β -Si₃N₄ Containing Y₂O₃ and Nd₂O₃. <u>J. Ceram. Soc. Japan</u>. Vol.100, No.6 (1992) : 826-829.
- 11. N. Hirosaki et al. Gas-Pressure Sintering of Low-Purity β -Si₃N₄ powder. <u>J. Ceram.</u> <u>Soc. Japan</u>. Vol.100, No.11 (1992) : 1366-1370.

- N. Hirosaki et al. Sintering of Y₂O₃-Al₂O₃-Doped β-Si₃N₄ Powder and Mechanical Properties of Sintered Materials. <u>J. Ceram. Soc. Japan</u>. Vol.102, No.8 (1994) : 790-794.
- 13. N. Hirosaki et al. Effect of Purification of β -Si₃N₄ Powder on the Strength of Sintered Materials. <u>J. Ceram. Soc. Japan</u>. Vol.103, No.6 (1995) : 639-643.
- 14. N. Hirosaki et al. Sintering of β -Si₃N₄ Powder Made by the Imide-Decomposition Method. <u>J. Ceram. Soc. Japan</u>. Vol.103, No.9 (1995) : 977-978.
- T. Ogasawara et al. Fatigue Behavior of Silicon Nitride Ceramics Prepared from β-Phase Powder. <u>J. Ceram. Soc. Japan</u>. Vol.103, No.7 (1995) : 709-712.
- Y. Okamoto et al. Mechanical Properties and Oxidation Resistance of Silicon Nitride Produced from Low Purity β-Powder. <u>J. Ceram. Soc. Japan</u>. Vol.103, No.7 (1995) : 720-723.
- M. Mitomo et al. Grain Growth During Gas-Pressure Sintering of β-silicon nitride.
 <u>J. Am. Ceram. Soc</u>. Vol.73, No.8 (1990) : 2441-2445.
- S. Wada et al. Sintering of Si₃N₄ Ceramics in Air Atmosphere Furnace. <u>J. Ceram.</u> <u>Soc. Japan</u>. Vol.109, No.3 (2001) : 281-283.
- Yet-Ming Chiang, Dunbar P. Birnie, and W. David Kingery. <u>Physical Ceramics</u>. New York : Jonh Wiley & Sons. Inc., 1997.
- F. L. Riley. Silicon nitride and related materials. <u>J. Am. Ceram. Soc</u>. Vol.83, No.2 (2000) : 245-265.
- 21. D. Hardie and K. H. Jack. <u>Nature</u>. Vol.180 (1957) : 332.
- G. Ziegler, J. Heinrich, and G. Wotting. Relationships between processing, microstructure and properties of dense and reaction-bonded silicon nitride.
 <u>J. Mater.Sci</u>. Vol.22 (1987) : 3041-3086.
- 23. S. Saito. Fine Ceramics. New York : Elsevier, 1988.
- 24. www.kyocera.com/kicc/industrial/types/index.htm
- G. Schwier. <u>Keramische Komponenten fur Fahrzeug-Gasturbinen</u>. Vol. 3, edited by W. Bunk, M. Bohmer and H. Kissler (Springer-Verlag, Berlin. (1984) : 55.
- S. T. Buljan and P. E. Stermer. <u>United State Patent</u>. Patent Number : 4073845, 1978.

- 27. M. Mori, H. Inoue and T. Ochiai, <u>Progress in Nitrogen Ceramics, edited by F.L.</u> <u>Riley,</u> (1983) : 149.
- T. Yamate, T. Kawahito and T. Iwai. <u>Proceedings of the International Symposium</u> on Ceramic Components for Engines, edited by S. Somiya, E. Kanai and K. Ando. Tokyo, (1983) : 333.
- C. Grekovich, J. H. Rosolowski. Sintering of covalent Solid. <u>J. Am. Ceram. Soc</u>. Vol.59, No.7-8 (1976) : 336-343.
- E. Proverbio, D. Rossi and R. Cigna. Influence of Water Vapour on Hightemperature Oxidation of Al₂O₃-MgO doped Hot-pressed Silicon Nitride. <u>J. Euro.</u> <u>Ceram. Soc</u>. Vol.9 (1992) : 453-458.
- 31. V. K. Sarin. On the α -to- β Phase Transformation in Silicon Nitride. <u>Mater. Sci.</u> Eng. A105/106 (1988) : 151-159.
- S. Wada. Control of Instability of Si₃N₄ during Pressureless Sintering. <u>J. Ceram.</u> <u>Soc. Japan</u>. Vol.109, No.10 (2001): 803-808
- C. Greskovich and S. Prochazka. Stability of Si₃N₄ and Liquid Phase (s) During Sintering. <u>J. Am. Ceram. Soc</u>. Vol.63 (1981) : C96-C97.
- 34. N. Hirosaki, Y. Akimune. Effect of Grain Growth of β-Silicon Nitride on Strength,
 Wiebull Modulus, and Fracture Toughness. J. Am. Ceram. Soc. Vol.76, No.7 (1993) : 1892-1894.
- 35. American Society for Testing and Material (ASTM). Standard test method for apparent porosity, liquid absorption, apparent specific gravity, and bulk density of refractory shapes by vacuum pressure. <u>ASTM C: 830-893</u>. New York : ASTM,1998.
- Japanese Industrials Standards (JIS). <u>Testing method for Vicker hardness of</u> <u>high performance ceramic</u>, JIS R 1610, 1991.
- Japanese Industrials Standards (JIS). <u>Testing method for toughness of high</u> performance ceramic, JIS R 1607, 1995.
- American Society for Testing and Material (ASTM). Standard test method for biaxial flexure strength (Modulus of rupture) of ceramic substrates. <u>ASTM F :</u> <u>394-78</u>. New York : ASTM, 1991.

- T. P. Herbell, Marc R. Freedman, and James D. Kiser. Particle-Size Reduction of Si₃N₄ Powder with Si₃N₄ Milling Hardware. <u>Ceram. Eng. Sci. Proc</u>. Vol.7, No.7-8 (1986).
- 40. S. Wada. Increase of oxygen content in Si_3N_4 powder during ball milling using alcohol as solvent. <u>J. Ceram. Soc. Japan</u>. Vol.104 (1996) : 1092-1094.
- Bongkoch Piempermpoon. <u>Improvement of thermal conductivity of alumina for</u> <u>Peltier element</u>. Master of science thesis, Department of Materials Science, Faculty of Science, Chulalongkorn University, 2002.
- 42. H. Scholze, Glastech. Ber.Vol.63 (1990) : 141-147.
- 43. R.G. Azrak and C.L. Angell, <u>J. Phys. Chem</u>. Vol.77 (1973) : 3048-3052.
- 44. Michel W. Barsoum. <u>Fundamentals of ceramics</u>. New York : McGraw-Hill Companies, Inc., 1997.
- 45. JANAF Thermochemical Table,2nd ed. U.S. Government printing office, Washington DC.,1971.
- 46. E.M. Levin, C.R. Lobbins, and H.F. Mcmurdie. <u>Phase Diagrams for Ceramists</u>. New York : Am. Ceram. Soc, 1964.
- Piyaporn Chaiyapuck. <u>Sintering of Silicon Nitride Ceramic in Air Furnace</u>. Master of science thesis, Department of Materials Science, Faculty of Science, Chulalongkorn University, 2003.
- 48. H. Wada, M.J. Wang, and T.Y. Tien. Stability of Phase in the Si-C-N-O System. J. Am. Ceram. Soc. Vol.71, No.10 (1988) : 837-840.
- 49. M. Mitomo et al. Effect of Atmosphere on the Reaction Sintering of Si_2N_2O . <u>Ceramics International</u>. Vol.15 (1989) : 345-350.
- 50. K. Yokoyama and S. Wada. Solid-Gas Reaction during Sintering of Si₃N₄ Ceramics (Part 3) : Mass losses in a Carbon Heater Furnace. <u>J. Ceram. Soc. Japan</u>. Vol.108, No.3 (2000) : 230-235.
- F.C. Peillon and F. thevenot. Microstructural designing of silicon nitride related to toughness. <u>J. Eur. Ceram. Soc</u>. Vol.22 (2002) : 271-278.
- 52. N. Hirosaki, and H. Matsubara. Effect of heat treatment of Si₃N₄ on grain growth behavior and grain boundary structure. <u>J. Ceram. Soc. Japan</u>. Vol.105 (1996) : 234 - 238.

53. G. Himsolt et al. Mechanical Properties of Hot-Pressed Silicon Nitride with Different Grain Structures. <u>J. Am. Ceram. Soc</u>. Vol.62, No.1-2 (1979) : 29 -32.



Appendices

Appendix A

Grade	SN-F2		
Beta-phase	100 %		
	Fe = 0.2 %		
Chemical composition	Na ⁺ = 5 ppm		
	Cl ⁻ = 1 ppm		
	Fe ⁺⁺ = 2010 ppm		
pH	9		
	+150 μm < 0.01 %		
Particle size	- 96 µm = 93 %		
3. 11 (a) (a)	- 48 µm = 66 %		
A REAL	D ₅₀ = 29 μm		

<u>Table A-1</u> Properties of Si_3N_4 powder

Table A-2 Properties of MgO used as additive

	Grade	MJ-30
ĺ	าถาบนาทย	MgO = 99.9
Q,		Fe = 0.0015
Ν	Chemical composition (%)	Si = 0.0031
		AI = 0.0011
		Ca = 0.0001
	Mean particle size (µm)	0.35

Grade	AKP-30		
	Al ₂ O ₃ = 99.99 %		
	Fe ≤ 20 ppm		
Chemical composition	Si ≤ 40 ppm		
	Na ≤ 10 ppm		
	Mg ≤ 10 ppm		
	Cu ≤ 10 ppm		
Packed bulk density	1.1~1.5 g/cm ³		
Loose bulk density	0.7~1.1 g/cm ³		
Mean particle size	0.4~0.6 µm		
Specific surface area	$4 \sim 6 \text{ m}^2/\text{g}$		

<u>Table A-3</u> Properties of Al_2O_3 used as an additive

<u>Table A-4</u> Properties of Al_2O_3 used as packing powder

Grade	A-11
Ŭ.	L.O.I = 0.01 %
J	Fe ₂ O ₃ = 0.01 %
Chemical composition	SiO ₂ = 0.01 %
สถาบบวิทย	Na ₂ O = 0.30 %
	Al ₂ O ₃ = 99.7 %
าลงกรณมห	H ₂ O = 0.06 %
True specific gravity	3.93 g/cm ³
Mean particle size	63 µm

Appendix B

Sieve number	Particle size	Weight of powder on sieve	Accumulate weight (%)
(mesh)	(µ m)	(%)	
50	300	0.03	0.03
100	150	14.86	14.89
140	106	7.15	22.04
200	75	11.43	33.47
230	63	6.16	39.63
325	45	9.46	49.09
400	38	5.00	54.09
Pan	< 38	45.91	100.00
Total		100.00	

Table B-1 Particle size of SN-F2 packing powder measured by sieve analysis



Fig B-1 Particle size distribution of SN-F2 packing powder measured by sieve analysis



Fig B-2 Accumulate weight of SN-F2 packing powder measured by sieve analysis



Appendix C

Calculation of equilibrium $P_{SiO (g)}$, $P_{Mg (g)}$, $P_{MgO (g)}$, $P_{Al2O(g)}$ and $P_{AlO (g)}$ as a function of temperature

In the previous work, it has been reported that the mass loss of Si_3N_4 during sintering comes from the reaction between Si_3N_4 (s) and SiO_2 (I) according to reaction (1).³²⁾

$$Si_3N_4(s) + 3 SiO_2(l) = 6 SiO(g) + 2 N_2(g)$$
 -----(1)

The equilibrium constant of the reaction, K_p , is calculated from the equation (2).

As the activity of a solid and liquid is 1. ⁴⁴⁾ Thus, the activity of Si_3N_4 , (a $_{Si3N4(s)}$) and SiO_2 , (a $_{SiO2(0)}$) is 1. Then:

$$K_{p} = P_{SiO(g)}^{6} \cdot P_{N2(g)}^{2}$$
 ------(3)

From equation (3), the partial pressure of the SiO (g) that is in equilibrium of equation (1) is determined by equation (4):

$$\Delta G = \Delta G^{\circ} + RT \ln K_{p} \qquad -----(4)$$

The other extreme occurs when the driving force for the reaction is zero, that is $\Delta G = 0 \text{ then}:$

$$0 = \Delta G^{\circ} + RT \ln K_{r}$$

$$lnK_p = -(\Delta G^{\circ}/RT)$$

As equation (6), ΔG° is the free energy changes that calculate from the free energy of each compound i (ΔG_i°). All ΔG_i° of each compound, which is Si₃N₄ (s), SiO₂ (I), N₂ (g) and SiO (g), are seen in the JANAF thermodynamic Table.⁴⁵⁾

$$\Delta G_{rxn}^{\circ} = \Delta G_{i}^{\circ}(\text{products}) - \Delta G_{i}^{\circ}(\text{reactants}) - \dots - (6)$$

In this case, assuming Partial pressure of N₂ gas, P_{N2(g)} is approximate 0.8 atm, because air includes 80 % of nitrogen. ¹⁸⁾ And R = 1.9872 Kcal.mol⁻¹.K⁻¹ is used. ⁴⁴⁾

Partial pressure of SiO gas, $P_{SiO (g)}$ calculate from take equation (3) into equation (5) Thus:

$$\log P_{SiO(g)}^{6} \cdot P_{N2(g)}^{2} = \frac{-\Delta G^{0}}{4.5767}$$

$$\log P_{SiO(g)}^{6} + \log P_{N2(g)}^{2} = \frac{-\Delta G^{0}}{4.5767}$$

$$6 \log P_{SiO (g)} = \frac{-\Delta G^0}{4.576T} - 2 \log (0.8)$$

 $\log P_{SiO (g)} = \left(\frac{\frac{1}{4.576T} \times (-\Delta G^{O} + 0.88T)}{6}\right)$ $P_{SiO (g)} = 10^{\left(\frac{1}{27.45T} \times (-\Delta G^{O} + 0.88T)\right)}$

As the same way, the gas partial pressure of Mg (g), MgO (g), Al_2O (g) and AlO (g) could be calculated from respectively reaction (7), (8), (9) and (10) by taken on equation (5). All of the calculation results are shown in Table C-1. In addition, the relationship between temperature (°C) and P_{SiO} (g), Mg (g), MgO (g), Al_2O (g) and AlO (g) are shown in Fig 1.

$$MgO(s) = Mg(g) + 1/2O_{2}(g) -----(7)$$

$$MgO(s) = MgO(g) -----(8)$$

$$Al_{2}O_{3}(s) = Al_{2}O(g) + O_{2}(g) -----(9)$$

$$2Al_{2}O_{3}(s) = 4AlO(g) + O_{2}(g) -----(10)$$

<u>TableC- 1</u> Calculation results of SiO (g), Mg (g), MgO (g), Al₂O (g) and AlO (g) partial pressure in equilibrium over Si_3N_4 at temperature range1500 °C to 1700 °C (1773 K to 1973 K)

Т	Т	Gases partial pressure (Pa)					
(°C)	(K)	P _{SiO (g)}	$P_{_{Mg}(\mathrm{g})}$	P _{MgO (g)}	P _{AI2O (g)}	P _{AIO (g)}	
1500	1773	7.8 × 10 ²	3.38 × 10 ⁻⁶	1.12 × 10 ⁻⁵	4.98 × 10 ⁻²⁰	4.28 × 10 ⁻¹⁰	
1550	1823	1.85 × 10 ³	1.32 × 10 ⁻⁵	3.41 × 10 ⁻⁵	8.69 × 10 ⁻¹⁹	2.30 × 10 ⁻⁹	
1600	1873	4.14×10^{3}	4.73 × 10 ⁻⁵	1.42 × 10 ⁻⁴	1.23 × 10 ⁻¹⁷	1.09 × 10 ⁻⁸	
1650	1923	8.92 × 10 ³	1.61 × 10 ⁻⁴	4.28 × 10 ⁻⁴	1.51 × 10 ⁻¹⁶	4.75 × 10 ⁻⁸	
1700	1973	1.84 × 10 ⁴	5.07 × 10 ⁻⁴	1.20 × 10 ⁻³	1.62 × 10 ⁻¹⁵	1.93 × 10 ⁻⁷	



<u>Fig C-1</u> Relationship between partial pressure of SiO (g), Mg (g), MgO (g), Al₂O (g) and AlO (g) as a function of temperature.



Appendix D

<u>Table D-1</u> Mass loss of Si $_3N_4$ specimens sintered in air atmosphere furnace at 1500, 1550, 1600, 1650 and 1700 °C for 2 h

Sample	Sample	Green weight	Sintered weight	Mass lo
code	number	(g)	(g)	(%)
E4H	1	2.0774	2.0846	-0.35
	2	2.1264	2.1404	-0.66
E6H	1	2.0526	2.0415	0.54
	2	2.0270	2.0195	0.37
E8H	1	2.0513	2.0347	0.81
	2	2.0219	2.0092	0.63
E10H	1	3.4462	3.3928	1.55
	2	3.5544	3.5000	1.53
E16H	1	3.4991	3.4247	2.13
	2	3.4663	3.3925	2.13
H10H	1	2.0275	1.9666	3.00
	2	2.0230	1.9693	2.65
H16H	1	2.0389	1.9603	3.86
	2	2.0015	1.9298	3.58
		Sintered at 1550	°C for 2 h	
Sample	Sample	Green weight	Sintered weight	Mass lo
code	number	(g)	(g)	(%)
E4H	1	2.0882	2.0824	0.28
	2	2.0718	2.0751	-0.16
E6H	1	2.0202	2.0082	0.59
	2	2.0654	2.0577	0.37
E8H	1	2.0486	2.0286	0.98
	2	2.0245	2.0066	0.88
E10H	1	3.4544	3.3984	1.62
	2	3.5472	3.4893	1.63
E16H	10	3.4993	3.4233	2.17
	2	3.5402	3.4651	2.12
	1	1.9820	1.9259	2.83
H10H		2 0200	1 9708	2.92
H10H	2	2.0500	1.7700	
H10H H16H	2	2.0300	1.9982	3.78

Sintered at 1600 °C for 2 h							
Sample	Sample	Green weight	Sintered weight	Mass loss			
code	number	(g)	(g)	(%)			
E4H	1	2.1035	2.0929	0.50			
	2	2.1237	2.1240	-0.01			
E6H	1	2.0127	1.9986	0.70			
	2	2.0139	2.0040	0.49			
E8H	1	2.0662	2.0452	1.02			
	2	2.0338	2.0168	0.84			
E10H	1	3.5112	3.4465	1.84			
	2	3.4934	3.4327	1.74			
E16H	1	3.515	3.4404	2.12			
	2	3.5299	3.4569	2.07			
H10H	1	2.0400	1.9791	2.99			
	2	2.0453	1.9876	2.82			
H16H	1	2.0296	1.9523	3.81			
	2	2.0318	1.9554	3.76			
		Sintered at 1650	°C for 2 h				
Sample	Sample	Green weight	Sintered weight	Mass loss			
code	number	(g)	(g)	(%)			
E4H	1/	2.0822	2.0712	0.53			
	2	2.1395	2.1350	0.21			
E6H	1	2.0297	2.0163	0.66			
	2	2.0573	2.0466	0.52			
E8H	1	2.0519	2.0311	1.01			
	2	2.0323	2.0145	0.88			
E10H	1	3.5149	3.4486	1.89			
	2	3.5623	3.4939	1.92			
E16H	1	3.5482	3.4665	2.30			
1	2	3.5173	3.4318	2.43			
H10H	1	2.0343	1.9726	3.03			
	2	2.0020	1.9449	2.85			
H16H	1	2.0106	1.9341	3.80			
	2	2.0195	1.9427	3.80			
		Sintered at 1700	°C for 2 h				
Sample	Sample	Green weight	Sintered weight	Mass loss			
code	number	(g)	(g)	(%)			
E4H	1	2.0327	2.0206	0.60			
14172	2	2.0633	2.0601	0.16			
E6H	1	2.0149	1.9995	0.76			
	2	2.0371	2.0264	0.53			
E8H	1	2.0363	2.0129	1.15			
	2	2.0158	1.9956	1.00			
E10H	1	3.4972	3.4295	1.94			
	2	3.5629	3.4989	1.80			
E16H	1	3.5354	3.4531	2.33			
	2	3.5733	3.4938	2.22			
H10H	1	2.0468	1.9869	2.93			
ļ	2	2.0112	1.9538	2.85			
H16H	1	1.9981	1.9227	3.77			
	2	2.0229	1.9471	3.75			

Table D-1 (cont.)

	Sintered at 1500 °C for 2 h							
Sample	Sample	D	S	W	W.A.	A.P.	B.D.	R.D.
code	number	(g)	(g)	(g)	(%)	(%)	(g/cm^3)	(%)
E4H	1	2.0846	1.4001	2.1750	4.34	11.67	2.68	83.23
	2	2.1404	1.4426	2.2424	4.77	12.75	2.67	82.80
E6H	1	2.0415	1.3569	2.0443	0.14	0.41	2.96	91.91
	2	2.0195	1.3376	2.0235	0.20	0.58	2.93	91.12
E8H	1	2.0347	1.3537	2.0360	0.06	0.19	2.97	92.58
	2	2.0092	1.3325	2.0111	0.09	0.28	2.95	91.92
E10H	1	3.393	2.2637	3.4089	0.47	1.39	2.95	92.87
	2	3.4998	2.3342	3.5239	0.69	2.03	2.93	92.21
E16H	1 🧹	3.4247	2.3356	3.4263	0.05	0.15	3.13	98.73
	2	3.3924	2.3173	3.3968	0.13	0.41	3.13	98.82
H10H	1	1.9666	1.3248	1.9674	0.04	0.12	3.05	96.51
	2	1.9693	1.3238	1.9709	0.08	0.25	3.03	95.97
H16H	1	1.9603	1.3177	1.9611	0.04	0.12	3.04	96.70
	2	1.9298	1.2974	1.9312	0.07	0.22	3.03	96.63
		S	intered at	1550 °C f	or 2 h			
Sample	Sample	D	S	W	W.A.	A.P.	B.D.	R.D.
code	number	(g)	(g)	(g)	(%)	(%)	(g/cm^3)	(%)
E4H	1	2.0824	1.3856	2.0911	0.42	1.23	2.94	91.32
	2	2.0751	1.3779	2.0879	0.62	1.80	2.91	90.43
E6H	1	2.0082	1.3690	2.0089	0.03	0.11	3.13	97.13
	2	2.0577	1.3999	2.0586	0.04	0.14	3.11	96.68
E8H	1	2.0286	1.3879	2.0293	0.03	0.11	3.15	98.19
	2	2.0066	1.3699	2.0075	0.04	0.14	3.14	97.70
E10H	1	3.3985	2.3165	3.4139	0.45	1.40	3.09	97.07
	2	3.4889	2.3794	3.5072	0.52	1.62	3.08	96.97
E16H	1	3.4232	2.3377	3.4291	0.17	0.54	3.13	98.63
	2	3.4647	2.3657	3.4721	0.21	0.67	3.12	98.47
H10H	1	1.9259	1.2958	1.9266	0.04	0.11	3.04	96.28
	2	1.9708	1.3242	1.9715	0.04	0.11	3.03	96.02
H16H	1	1.9982	1.3505	1.9991	0.05	0.14	3.07	97.77
ลา	2	1.9539	1.3180	1.9549	0.05	0.16	3.06	97.36

<u>Table D-2</u> Water absorption, apparent porosity and density of Si_3N_4 specimens sintered in air atmosphere furnace at 1500, 1550, 1600, 1650 and 1700 °C for 2 h

Table D-2 (cont.)

	Sintered at 1600 °C for 2 h							
Sample	Sample	D	S	W	W.A.	A.P.	B.D.	R.D.
code	number	(g)	(g)	(g)	(%)	(%)	(g/cm^3)	(%)
E4H	1	2.0929	1.4176	2.0961	0.15	0.47	3.07	95.44
	2	2.1240	1.4336	2.1264	0.11	0.35	3.05	94.86
E6H	1	1.9986	1.3649	1.9992	0.03	0.09	3.14	97.51
	2	2.0040	1.3672	2.0046	0.03	0.09	3.13	97.30
E8H	1	2.0452	1.3984	2.0461	0.04	0.14	3.15	98.03
	2	2.0168	1.3732	2.0181	0.06	0.20	3.12	97.09
E10H	1	3.4 <mark>193</mark>	2.3359	3.4261	0.20	0.62	3.13	98.31
	2	3.4326	2.3443	3.4479	0.45	1.39	3.10	97.50
E16H	1	3.4401	2.3513	3.4446	0.13	0.41	3.14	98.94
	2	3.4564	2.3653	3.4649	0.25	0.77	3.13	98.84
H10H	1	1.9791	1.3369	1.9799	0.04	0.12	3.07	97.07
	2	1.9876	1.3407	1.9886	0.05	0.15	3.06	96.75
H16H	1	1.9523	1.3177	1.9531	0.04	0.13	3.06	97.51
	2	1.9554	1.3132	1.9562	0.04	0.12	3.03	96.51
		Si	ntered at 1	650 °C for	r 2 h			
Sample	Sample	D	S	W	W.A.	A.P.	B.D.	R.D.
code	number	(g)	(g)	(g)	(%)	(%)	(g/cm^3)	(%)
E4H	1	2.0712	1.4059	2.0729	0.08	0.25	3.09	96.08
	2	2.1350	1.4476	2.1366	0.07	0.23	3.09	95.87
E6H	1	2.0163	1.3776	2.0171	0.04	0.13	3.14	97.58
	2	2.0466	1.3958	2.0478	0.06	0.18	3.13	97.15
E8H	1	2.0311	1.3882	2.0331	0.10	0.31	3.14	97.78
	2	2.0145	1.3750	2.0154	0.04	0.15	3.13	97.66
E10H	1	3.4482	2.3573	3.4578	0.28	0.87	3.12	98.26
	2	3.4933	2.3856	3.5013	0.23	0.72	3.12	98.18
E16H	1	3.4662	2.372	3.4706	0.13	0.40	3.15	99.25
	2	3.4317	2.3488	3.4381	0.19	0.59	3.14	99.10
H10H	1	1.9726	1.3321	1.9734	0.04	0.14	3.07	97.00
	2	1.9449	1.3109	1.9459	0.05	0.18	3.05	96.59
H16H	1	1.9341	1.2999	1.9349	0.04	0.13	3.04	96.67
	2	1.9427	1.3035	1.9455	0.14	0.44	3.02	96.04

Sintered at 1700 °C for 2 h								
Sample	Sample	D	S	W	W.A.	A.P.	B.D.	R.D.
code	number	(g)	(g)	(g)	(%)	(%)	(g/cm^3)	(%)
E4H	1	2.0206	1.3740	2.0230	0.12	0.37	3.10	96.33
	2	2.0601	1.3977	2.0632	0.15	0.47	3.08	95.78
E6H	1	1.9995	1.3648	2.0015	0.10	0.31	3.13	97.19
	2	2.0264	1.3810	2.0285	0.10	0.32	3.12	96.86
E8H	1	2.0129	1.3759	2.0149	0.10	0.31	3.14	97.79
	2	1.9956	1.3616	1.9968	0.06	0.18	3.13	97.53
E10H	1	3.42 <mark>95</mark>	2.342	3.4345	0.15	0.46	3.13	98.44
	2	3.499	2.3875	3.5017	0.08	0.24	3.13	98.48
E16H	1	3.4535	2.3616	3.4556	0.06	0.19	3.15	99.30
	2	3.4937	2.3862	3.4987	0.14	0.45	3.13	98.79
H10H	1	1.9869	1.3413	1.9886	0.09	0.25	3.06	96.80
	2 🧹	1.9538	1.3166	1.9544	0.03	0.09	3.05	96.61
H16H	1	1.9227	1.2913	1.9237	0.05	0.16	3.03	96.49
	2	1.9471	1.3054	1.9478	0.04	0.11	3.02	96.19

Table D-2 (cont.)

Note:

= Dry weight

D

- S = Suspended weight in water
- W = Saturated weight
- W.A. = Water absorption
- A.P. = Apparent porosity
- B.D. = Bulk density
- R.D. = Relative density

Sintered at 1750 °C for 2 h							
Sample	Sample	Green weight	Sintered weight	Mass loss			
code	number	(g)	(g)	(%)			
E4H	1	4.4841	4.3732	2.47			
	2	4.5209	4.3820	3.07			
E6H	1	4.4690	4.3456	2.76			
	2	4.5372	4.3861	3.33			
	1	4.5387	4.3886	3.31			
E8H	2	4.5157	4.3722	3.18			
	3	4.5388	4.3815	3.47			
	S	Sintered at 1800 °	C for 2 h				
Sample	Sample	Green weight	Sintered weight	Mass loss			
code	number	(g)	(g)	(%)			
E4H	1	4.5104	4.3254	4.10			
	2	4.5033	4.2553	5.51			
E6H	1	4.5157	4.3087	4.58			
	2	4.4473	4.1825	5.95			
	1	4.5322	4.2945	5.24			
E8H	2	4.5540	4.3448	4.59			
	3	4.4979	4.2599	5.29			

<u>Table D-3</u> Mass loss of Si $_3N_4$ specimens sintered in N_2 atmosphere furnace at 1750 and 1800 $^\circ\text{C}$ for 2 h



Sintered at 1750 °C for 2 h									
Sample	Sample	D	S	W	W.A.	A.P.	B.D.	R.D.	
code	number	(g)	(g)	(g)	(%)	(%)	(g/cm^3)	(%)	
E4H	1	4.3732	2.9944	4.3773	0.09	0.30	3.15	97.87	
	2	4.3820	3.0030	4.3859	0.09	0.28	3.16	98.07	
E6H	1	4.3456	2.9814	4.3498	0.10	0.31	3.16	98.28	
	2	4.3861	3.0099	4.3905	0.10	0.32	3.17	98.32	
	1	4.3886	3.0138	4.3929	0.10	0.31	3.17	98.79	
E8H	2	4.3722	3.0021	4.3777	0.13	0.40	3.17	98.67	
	3	4.3815	3.0091	4.3864	0.11	0.36	3.17	98.76	
Sintered at 1800 °C for 2 h									
Sample	Sample	D	S	W	W.A.	A.P.	B.D.	R.D.	
code	number	(g)	(g)	(g)	(%)	(%)	(g/cm^3)	(%)	
E4H	1	4.3254	2.9859	4.3302	0.11	0.36	3.21	99.58	
	2	4.2553	2.9202	4.2613	0.14	0.45	3.16	98.20	
E6H	1	4.3087	2.9587	4.3160	0.17	0.54	3.16	98.24	
	2	4.1825	2.8751	4.1888	0.15	0.48	3.17	98.53	
	1	4.2945	2.9516	4.3005	0.14	0.44	3.17	98.84	
E8H	2	4.3448	2.9845	4.3504	0.13	0.41	3.17	98.75	
	3	4.2599	2.9268	4.2657	0.14	0.43	3.17	98.77	

<u>Table D-4</u> Water absorption, apparent porosity and density of Si_3N_4 specimens sintered in $\rm N_2$ gas furnace at 1750 and 1800 $^{\circ}\rm C$ for 2 h

Note: D =	Dry weight
-----------	------------

=

S

- Suspended weight in water
- W Saturated weight =
- W.A. Water absorption =

- Apparent porosity A.P. =
- B.D. = Bulk density
- R.D. = Relative density





<u>Fig E-1</u> X-ray diffraction pattern of Si_3N_4 raw powder (SN-F2)







d/straftmatsc/Wiruft/E6H1500.RAW - File: E6h1500.raw - Type: 2Th/Th locked - Start: 10.000 * - End: 70.000 * - Step: 0.040 * - Step time: 1. s - Temp.: 25 *C (Room) - Time St 929-1132 (D) - Silicon Nitride - Si3N4 - Y: 50.00 % - d x by: 1. - WL: 1.5406 - 0 - I/Ic PDF 1.1 -



Contended Contended
 Contended Contended
 Contended Contended Contended
 Contended Contend Contended Contended Contended Contended





Wid /urd/matsci/Niu/E4H1700 RAW - File: E4h1700.raw - Type: 2Th/Th locked - Start: 10.000 * - End: 70.000 * - Step: 0.040 * - Step time: 1, s - Temp: 25 *C (Room) - Time St
 E:29-1132 (D) - Silicon Nitride - Si3N4 - Y: 50.00 % - d x by: 1. + WL: 1.5408 + 0 - I/lo PDF 1.1 -







d:/vrd/matsci/Nirutl+16H1650.RAW - File: H16h1650.raw - Type: 2Th/Th locked - Start: 10.000 * - End: 70.000 * - Step: 0.040 * - Step time: 1. s - Temp.: 25 *C (Room) - Time
 29-1132 (D) - Silicon Nitride - Si3N4 - Y: 50.00 % - d x by: 1. - WL: 1.5406 - 0 - I/lc PDF 1.1 18-1171 (D) - Sinoite, syn - Si2N2O - Y: 9.55 % - d x by: 1. - WL: 1.5406 - 0 -



d: Vard'matsci/Nirut/E6H1800.RAW - File: E6h1800.raw - Type: 2Th/Th locked - Start: 10.000 * - End: 70.000 * - Step: 0.040 * - Step time: 1. s - Temp.: 25 °C (Room) - Time St
29-1132 (D) - Silicon Nitride - Si3N4 - Y: 50.00 % - d x by: 1. - WL: 1.5406 - 0 - I/ic PDF 1.1 -

Appendix F



<u>Fig F-1</u> SEM micrograph of E8H specimens sintered in air furnace at various temperatures; (a) 1550 $^{\circ}$ C, (b) 1600 $^{\circ}$ C



(c)

<u>Fig F-1</u> (cont.) SEM micrograph of E8H specimens sintered in air furnace at various temperature; (c) 1700 $^{\circ}$ C



(a)



(b)

<u>Fig F-2</u> SEM micrograph of H16H specimens sintered in air furnace at various temperature; (a) 1550 $^{\circ}$ C, (b) 1600 $^{\circ}$ C



(C)

<u>Fig F-2</u> (cont.) SEM micrograph of H16H specimens sintered in air furnace at various temperature; (c) 1700 $^{\circ}$ C


(a)



<u>Fig F-3</u> SEM micrograph of E4H specimens sintered in N_2 gas furnace; (a) 1750 $^{\circ}$ C, (b) 1800 $^{\circ}$ C



(a)



<u>Fig F-4</u> SEM micrograph of E6H specimens sintered in $\rm N_2$ gas furnace; (a) 1750 $^{\rm o}\rm C$, (b) 1800 $^{\rm o}\rm C$

Appendix G

Sample	Sample No.	2a	С	Hv	K _{IC}
code	(Piece)	(µm)	(µm)	(GPa)	(MPa m ^{1/2})
	1	119.33	125.90	12.8	6.1
	2	118.76	122.06	12.9	6.3
E4H	3	119.76	129.74	12.7	5.8
	4	120.86	127.55	12.5	6.0
	5	120.31	141.37	12.6	5.1
Average				12.7	5.9
S.D.				0.2	0.4
	1	117.76	122.52	13.1	6.2
	2	120.45	125.46	12.5	6.1
E6H	3	118.05	120.39	13.1	6.4
	4	117.36	127.46	13.2	5.8
	5	118.64	129.60	12.9	5.8
Average				13.0	6.1
S.D.				0.3	0.3
	1	121.05	138.25	12.4	5.3
	2	120.86	133.25	12.5	5.6
E8H	3	118.83	135.44	12.9	5.4
	4	118.98	135.18	12.8	5.4
	5	119.62	134.37	12.7	5.5
Average				12.7	5.5
S.D.	การเรา	างกย	ปรถา	0.2	0.1

<u>Table G-1</u> Results of fracture toughness (K_{IC}) and Vickers hardness (Hv) of sintered specimens at 1700 $^{\circ}$ C for 2 h, in air furnace.

จุฬาลงกรณมหาวิทยาลย

Sample	Sample No.	2a	С	Hv	K _{IC}
code	(Piece)	(µm)	(µm)	(GPa)	(MPa m ^{1/2})
	1	117.45	113.30	13.2	7.0
	2	116.93	113.01	13.3	7.0
E4H	3	116.36	112.67	13.4	7.0
	4	116.17	107.45	13.5	7.5
	5	117.00	130.88	13.3	5.6
Average				13.3	6.8
S.D.				0.1	0.7
	1	113.90	122.46	14.0	6.0
	2	115.64	113.58	13.6	6.8
E6H	3	115.14	114.60	13.7	6.7
	4	115.17	117.19	13.7	6.5
	5	115.45	121.20	13.6	6.2
Average				13.7	6.5
S.D.		3. 56.050		0.2	0.3
	1	116.74	130.31	13.3	5.6
	2	116.00	119.38	13.5	6.4
E8H	3	116.67	120.52	13.4	6.3
	4	117.38	121.85	13.2	6.3
	5	115.86	126.30	13.5	5.9
Average	SAL			13.4	6.1
S.D.			1	0.1	0.3

<u>Table G-2</u> Results of fracture toughness (K_{IC}) and Vickers hardness (Hv) of sintered specimens at 1750 $^{\circ}$ C for 2 h, in N₂ furnace.

Sample	Sample No.	2a	С	Hv	K _{IC}
code	(Piece)	(µm)	(µm)	(GPa)	(MPa m ^{1/2})
	1	115.98	115.05	13.5	6.7
	2	113.64	110.39	14.1	7.0
E4H	3	115.29	115.94	13.7	6.6
	4	115.31	130.65	13.7	5.5
	5	117.64	110.90	13.1	7.2
Average				13.6	6.6
S.D.			1	0.3	0.7
	1	115.05	114.27	13.7	6.8
	2	114.91	122.22	13.8	6.1
E6H	3	114.95	130.92	13.8	5.5
	4	114.25	106.37	13.9	7.5
	5	115.09	119.86	13.7	6.3
Average				13.8	6.4
S.D.		A A A A	1.	0.1	0.7
	1	114.39	114.17	13.9	6.7
	2	121.04	113.94	12.4	7.1
E8H	3	115.52	112.55	13.6	6.9
	4	115.66	116.09	13.6	6.6
	5	115.05	115.78	13.7	6.6
Average				13.5	6.8
S.D.				0.6	0.2

<u>Table G-3</u> Results of fracture toughness (K_{IC}) and Vickers hardness (Hv) of sintered specimens at 1800 $^{\circ}$ C for 2 h, in N₂ furnace.

Calculation results of specimens sintered in air and $\mathrm{N}_{\!_2}$ atmosphere furnace

The calculation results of biaxial flexural strength were calculated using the equation as follows:

S =
$$\frac{-0.2387 P \times (X - Y)}{d^2}$$

Table G-4Calculation results of biaxial flexural strength (S) of specimens sintered at1650 °C for 2 h, in air furnace

Sample	Sample	Diameter	Thickness	X	Y	d^2	Р	S
code	number	(mm)	(mm)			(mm^2)	(N)	(MPa)
	1	<mark>26.84</mark>	1.321	-4.121	1.723	1.745	292.2	234
	2	2 <mark>6.8</mark> 4	1.321	-4.121	1.723	1.745	274.8	220
E10H	3	26.84	1.321	-4.121	1.723	1.745	250.4	200
	4	26. <mark>84</mark>	1.321	-4.121	1.723	1.745	241.3	193
	5	26.84	1.321	-4.121	1.723	1.745	251.8	201
	6	26.84	1.321	-4.121	1.723	1.745	387.6	310
	7	26.84	1.321	-4.121	1.723	1.745	263.8	211
	8	26.84	1.321	-4.121	1.723	1.745	245.7	196
	9	26.84	1.321	-4.121	1.723	1.745	259.4	207
Average								219
S.D.								36

Sample	Sample	Diameter	Thickness	Х	Y	d^2	Р	S
code	number	(mm)	(mm)			(mm^2)	(N)	(MPa)
	1	27.88	1.475	-4.215	1.581	2.176	358.8	228
	2	27.88	1.475	-4.215	1.581	2.176	409.5	260
E4H	3	27.95	1.466	-4.222	1.570	2.149	319.3	205
	4	28.18	1.474	-4.242	1.541	2.173	431.4	274
	5	27.95	1.475	-4.219	1.576	2.176	370.8	236
	6	27. <mark>95</mark>	1.461	-4.222	1.570	2.135	345.0	223
Average								238
S.D.								25
	1	27.75	1.456	-4.167	1.602	2.120	342.9	223
	2	27.68	1.475	-4.197	1.608	2.176	408.6	260
E6H	3	27.63	1.471	-4.192	1.616	2.164	521.3	334
	4	27.73	1.471	-4.201	1.602	2.164	419.8	269
	5	27.93	1.462	-4.219	1.576	2.137	351.7	228
Average								263
S.D.			3. 1. 1. 1.					45
	1	<mark>27.73</mark>	1.472	-4.201	1.602	2.167	393.5	252
	2	27 <mark>.5</mark> 5	1.469	-4.186	1.624	2.158	374.8	241
E8H	3	27.50	1.468	-4.181	1.632	2.155	306.9	198
	4	27.55	1.466	-4.186	1.624	2.149	352.7	228
	5	27.48	1.460	-4.179	1.635	2.132	424.6	276
	6	27.48	1.433	-4.179	1.635	2.053	474.0	320
Average								252
S.D.								42

<u>Table G-5</u> Calculation results of biaxial flexural strength (S) of specimens sintered at 1700 $^{\circ}$ C for 2 h, in air furnace

	Sintering at 1750 °C for 2 h								
Sample	Sample	Diameter	Thickness	Х	Y	d^2	Р	S	
code	number	(mm)	(mm)			(mm ²)	(N)	(MPa)	
E4H	1	26.90	2.407	-4.126	1.715	5.794	1647.0	396	
	2	26.62	2.415	-4.100	1.755	5.832	1734.0	416	
Average	ge								
S.D.								14	
E6H	1	26.62	2.474	-4.100	1.755	6.121	1585.0	362	
	2	26.70	2.475	-4.108	1.743	6.126	1285.0	293	
Average								327	
S.D.						1		49	
	1	27.15	2.408	-4.149	1.680	5.798	1343.0	322	
E8H	2	26.70	2.443	-4.108	1.743	5.968	1751.0	410	
	3	27.00	2.405	-4.135	1.701	5.784	1050.0	253	
Average								328	
S.D.			1000					79	
	1		Sintering at 1	800 °C fo	r 2 h	1			
Sample	Sample	Diameter	Thickness	Х	Y	d2	Р	S	
code	number	(mm)	(mm)	5556		(mm2)	(N)	(MPa)	
E4H	1	26.98	2.369	-4.133	1.704	5.612	1369.0	340	
	2	26.80	2.362	-4.117	1.729	5.579	1097.0	274	
Average								307	
S.D.								46	
E6H	1	26.65	2.427	-4.103	1.750	5.890	1205.0	286	
	2	26.56	2.357	-4.094	1.763	6.126	1039.0	237	
Average								261	
S.D.	- 35	22919	1091	01914	ຮຸ	25		34	
	1	26.42	2.450	-4.081	1.784	6.003	1683.0	393	
E8H	2	26.52	2.383	-4.091	1.769	5.679	1836.0	452	
	3	26.48	2.413	-4.087	1.775	5.823	1354.0	325	
Average								390	
S.D.								63	

<u>Table G-6</u> Calculation results of biaxial flexural strength (S) of specimens sintered at 1750 °C and 1800 °C for 2 h, in air furnace

Appendix H

Properties of TOSHIBA's specimen (standard bar)

1. Chemical composition

Composition (mass %)								
$\mathrm{Si}_{3}\mathrm{N}_{4}$	MgAl ₂ O ₄	SiC	SiO ₂	TiO ₂				
88.9	4.3	5.0	0.9	0.9				

2. Estimated real density: 3.23 g/cm³

Densities of Si_3N_4 , $MgAl_2O_4$, SiC, SiO_2 , and TiO_2 are 3.21, 3.60, 3.22, 2.20 and 4.25 g/cm³, respectively.

- Bulk density and relative density
 Measured bulk density was 3.19 g/cm³. Then, relative density is 98.8 %
- 4. Vickers' Hardness

16.8 GPa

- Fracture Toughness
 5.4 (MPa.m^{1/2})
- 6. Young's Modulus, E = 300 GPa.

BIOGRAPHY

Mr. Nirut Wangmooklang was born in Nakhonratchasima on 24th November 1977. He was received a Bachelor's Degree in Chemistry from Faculty of Science and Technology, Rajabhat Institute Bansomdejchaopraya in 2001. During his Bachelor study, he was also working at Siam Research and Development Co. Ltd. After working for 3 years, he continued studying in Master's Degree in the field of Ceramic Technology at Chulalongkorn University and graduated in April 2004.

